

## TPS657095 用于嵌入式摄像头模块的电源管理单元 (PMU)

### 1 特性

- 2 个 100mA 低压降稳压器 (LDO)
- 输出电压精度为  $\pm 1.5\%$
- $V_{IN}$  范围为 3.7V 至 6V
- 具有 PWM 调光功能的 LED 驱动器
- 1 GPO
- 1 个 GPIO
- I<sup>2</sup>C™ 接口
- 4KB 用户一次性可编程 (OTP) 存储器
- 采用 16 焊球 0.4mm 间距芯片尺寸球栅阵列封装 (DSBGA)

### 2 应用

- 笔记本电脑
- 可拆卸平板电脑
- 平板电脑
- 监视器
- 智能手机

### 3 说明

TPS657095 是面向嵌入式摄像头模块或其他便携式低功耗消费类终端设备的电源管理单元。其包含两个由 I<sup>2</sup>C™ 接口使能的 LDO、一个用于驱动单个发光二极管 (LED) 的脉宽调制 (PWM) 可调光电流阱、一个通用输出 (GPO)、一个可编程时钟发生器和 4KB 的用户 OTP 存储器。如果输入电压电源低于内部欠压锁定值，则该器件将被禁止运行。

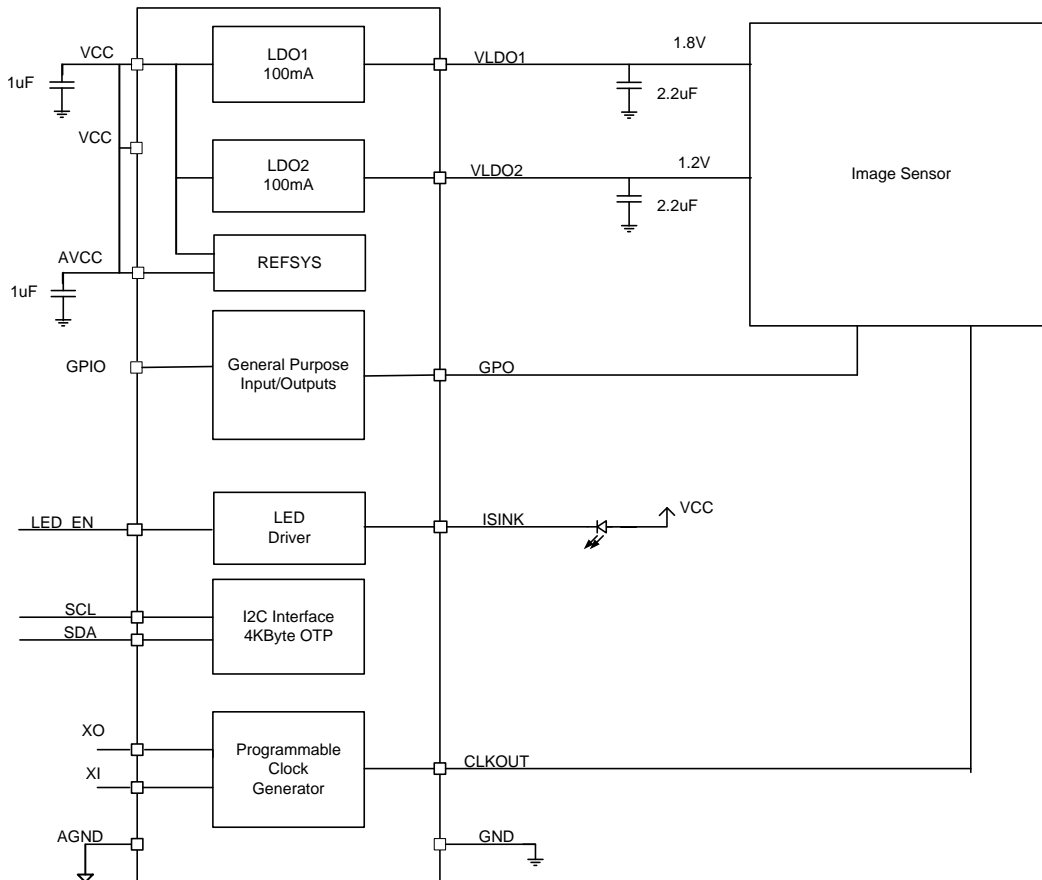
此器件采用 16 焊球芯片尺寸球栅阵列封装 (DSBGA)，焊球间距为 0.4mm。

#### 器件信息<sup>(1)</sup>

器件型号	封装	封装尺寸 (标称值)
TPS657095	DSBGA (16)	1.70mm x 1.70mm

(1) 要了解所有可用封装，请见数据表末尾的可订购产品附录。

#### 应用电路



## 目录

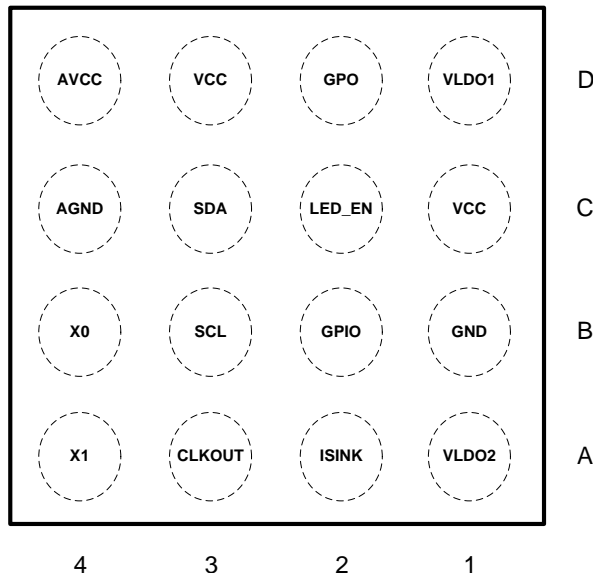
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## 4 修订历史记录

日期	修订版本	注释
2015 年 9 月	*	首次发布。

## 5 Pin Configuration and Functions

**YFF Package  
16-Pin DSBGA  
Top View**



**Pin Functions**

PIN		I/O	DESCRIPTION
NAME	NUMBER		
VCC	C1, D3	I	Supply Input. Connect a 1uF cap close to the C1 pin. Connect pins C1 and D3 together externally.
GND	B1	I	Ground connection (main device ground - connect to ground plane on PCB)
AVCC	D4	I	Analog Supply Input. Connect a 1uF cap close to pin. The D4 pin must be connected externally to the D3 and C1 pins.
AGND	C4	I	Analog Ground connection (device quiet ground - connect to ground plane on PCB)
VLDO1	D1	O	Output voltage from LDO1
VLDO2	A1	O	Output voltage from LDO2
ISINK	A2	O	Open drain current sink; connect to the cathode of LED
GPO	D2	O	general purpose output
LED_EN	C2	I	LED enable pin ( 0 = disabled, 1 = enabled)
GPIO	B2	I	General Purpose Input/Output (see GPIO_CTRL Register for details) As an input, it is used to enable LDO2
SCL	B3	I	clock input for the I2C compatible interface
SDA	C3	I/O	data input for the I2C compatible interface
XO	B4	I	connection for external crystal to clock generator (input of amplifier)
XI	A4	I	connection for external crystal to clock generator (output of amplifier)
CLKOUT	A3	O	clock output

## 6 Specifications

### 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

		MIN	MAX	UNIT
Voltage	All pins except GND pin with respect to AGND	-0.3	7	V
	GPIO and GPO pull-up voltage if configured as open drain output	-0.3	V <sub>CC</sub> + 0.3	V
	Pin VLDO1 and VLDO2 with respect to AGND	-0.3	3.6	V
Current	VLDO1, VLDO2, VCC		200	mA
	GND, ISINK, GPIO, GPO		50	mA
	All other pins		3	mA
Operating free-air temperature, T <sub>A</sub>		-40	85	°C
Maximum junction temperature, T <sub>J</sub>			125	°C
Storage temperature range, T <sub>stg</sub>		-65	150	°C

- (1) Stresses beyond those listed under *absolute maximum ratings* may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under *recommended operating conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

### 6.2 ESD Ratings

			VALUE	UNIT
V <sub>(ESD)</sub>	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 <sup>(1)</sup>	2000	V
		Charged device model (CDM), per JEDEC specification JESD22-C101 <sup>(2)</sup>	500	V

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.  
 (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

### 6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V <sub>CC</sub> /AV <sub>CC</sub>	Input voltage range	3.7		6	V
C <sub>VCC</sub>	Input capacitor at V <sub>CC</sub>	1			μF
C <sub>AVCC</sub>	Input capacitor at AV <sub>CC</sub>	1			μF
V <sub>LDOx</sub>	Output voltage range for LDO1 and LDO2	0.8		3.3	V
I <sub>LDO</sub>	Output current at LDO1 or LDO2			75	mA
C <sub>OUTLDO1/2</sub>	Output capacitance at V <sub>LDO1</sub> , V <sub>LDO2</sub>	2.2		6.8	μF
LED_EN	Voltage range	1.3		6	V
GPIO	Voltage range (configured as an input)	1.3		3.3	V
T <sub>A</sub>	Operating ambient temperature	-40		85	°C
T <sub>J</sub>	Operating junction temperature	-40		125	°C

### 6.4 Thermal Information

THERMAL METRIC <sup>(1)</sup>		TPS657095	UNIT
		YFF (DSBGA)	
		16 PINS	
R <sub>θJA</sub>	Junction-to-ambient thermal resistance	78.2	°C/W
R <sub>θJC(top)</sub>	Junction-to-case (top) thermal resistance	0.6	
R <sub>θJB</sub>	Junction-to-board thermal resistance	13.2	
Ψ <sub>JT</sub>	Junction-to-top characterization parameter	2.5	
Ψ <sub>JB</sub>	Junction-to-board characterization parameter	13	
R <sub>θJC(bot)</sub>	Junction-to-case (bottom) thermal resistance	n/a	

- (1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, [SPRA953](#).

## 6.5 Electrical Characteristics

Unless otherwise noted:  $V_{CC} = AV_{CC} = 5V$ ,  $C_{VCC} = 1\mu F$ ;  $C_{OUTLDOx} = 2.2\mu F$ ,  $T_A = -40^\circ C$  to  $85^\circ C$

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>SUPPLY CURRENT</b>						
$V_{CC}$ , $AV_{CC}$	Supply voltage	During normal operation	3.7		6	V
		During programming (writing) of OTP memory	-5%	5	+5%	V
$I_Q$	Operating quiescent current	LDO1 disabled LDO2 disabled No I <sup>2</sup> C communications LED_EN = 0 CLKout_EN = 0 24MHz crystal disabled		25	30	$\mu A$
		LDO1 disabled LDO2 enabled, $I_{OUT(LDO2)} = 0$ mA No I <sup>2</sup> C communications LED_EN = 0 CLKout_EN = 0 24MHz crystal disabled		40	55	$\mu A$
		LDO1 enabled, $I_{OUT(LDO1)} = 0$ mA LDO2 disabled No I <sup>2</sup> C communications LED_EN = 0 CLKout_EN = 0 24MHz crystal disabled		40	55	$\mu A$
		LDO1 enabled, $I_{OUT(LDO1)} = 0$ mA LDO2 enabled, $I_{OUT(LDO2)} = 0$ mA No I <sup>2</sup> C communications LED_EN = 0 CLKout_EN = 0 24MHz crystal disabled		60	80	$\mu A$
		LDO1 enabled, $I_{OUT(LDO1)} = 0$ mA LDO2 enabled, $I_{OUT(LDO2)} = 0$ mA No I <sup>2</sup> C communications LED_EN = 0 CLKout_EN = 1 24MHz crystal enabled		2900	3550	$\mu A$
		LDO1 enabled, $I_{OUT(LDO1)} = 0$ mA LDO2 enabled, $I_{OUT(LDO2)} = 0$ mA No I <sup>2</sup> C communications LED_EN = 1, PWM Duty Cycle set to 99.9%, ISINK = 2mA CLKout_EN = 1 24MHz crystal enabled		3000	3600	$\mu A$
$I_{SD}$	Shutdown current	Device disabled; $V_{CC}$ and $AV_{CC} < 1.8V$		45	85	$\mu A$
<b>LED_ENABLE</b>						
$V_{IH}$	High level input voltage		1.1		$V_{CC}$	V
$V_{IL}$	Low level input voltage				0.4	V
$I_{(in)lk}$	Input Leakage Current				0.1	$\mu A$
	Input Deglitch	With a minimum pulse period of 500ns before another glitch is received			100	ns
<b>GENERAL PURPOSE INPUT/OUTPUT (GPIO)</b>						
$V_{IH}$	High level input voltage	For VLDO1 = 1.8V	1.1		VLDO1	V
$V_{IH}$	High level input voltage	For VLDO1 = 3.3V	1.37		VLDO1	V
$V_{IL}$	Low level input voltage	For VLDO1 = 1.8V	0		0.4	V
$V_{IL}$	Low level input voltage	For VLDO1 = 3.3V	0		0.6	V
$I_{(in)lk}$	Input leakage current	GPIO programmed as input and tied to GND or $V_{CC}$		0.01	0.1	$\mu A$
$V_{OH}$	High level output voltage	Configured as a push-pull output, $I_{OH} = 1mA$ , VLDO1 $\geq 1.8V$	1.2	$V_{LDO1} - 0.2V$	$V_{LDO1}$	V

**Electrical Characteristics (continued)**

 Unless otherwise noted:  $V_{CC} = AV_{CC} = 5V$ ,  $C_{VCC} = 1\mu F$ ;  $C_{OUTLDOX} = 2.2\mu F$ ,  $T_A = -40^{\circ}C$  to  $85^{\circ}C$ 

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
$V_{OH}$	High level output voltage	Configured as a push-pull output, $I_{OH} = 1mA$ , $1.3V \leq VLDO1 \leq 1.8V$	1.0		$V_{LDO1}$	V
$V_{OL}$	Low level output voltage	Configured as a push-pull output, $I_{OL} = 2mA$ , $VLDO1 \geq 1.8V$			0.25	V
$V_{OL}$	Low level output voltage	Configured as a push-pull output, $I_{OL} = 2mA$ , $1.3V \leq VLDO1 \leq 1.8V$			0.3	V
$V_{OL}$	Low level output voltage	Configured as an open-drain output, $I_{OL} = 4mA$ , $VLDO1 \geq 1.8V$			0.6	V
$V_{OL}$	Low level output voltage	Configured as an open-drain output, $I_{OL} = 2mA$ , $1.3V \leq VLDO1 \leq 1.8V$			0.6	V
$I_{(out)lkG}$	Output leakage current	Configured as an open-drain output, GPIO connected to VLDO1		0.01	0.1	$\mu A$
<b>GENERAL PURPOSE OUTPUT (GPO)</b>						
$V_{OH}$	High level output voltage	Configured as a push-pull output, $I_{OH} = 1mA$ , $VLDO1 \geq 1.8V$	1.2	$V_{LDO1} - 0.2V$	$V_{LDO1}$	V
$V_{OH}$	High level output voltage	Configured as a push-pull output, $I_{OH} = 1mA$ , $1.3V \leq VLDO1 \leq 1.8V$	1.0		$V_{LDO1}$	V
$V_{OL}$	Low level output voltage	Configured as a push-pull output, $I_{OL} = 2mA$ , $VLDO1 \geq 1.8V$			0.25	V
$V_{OL}$	Low level output voltage	Configured as a push-pull output, $I_{OL} = 2mA$ , $1.3V \leq VLDO1 \leq 1.8V$			0.3	V
$V_{OL}$	Low level output voltage	Configured as an open-drain output, $I_{OL} = 4mA$ , $VLDO1 \geq 1.8V$			0.6	V
$V_{OL}$	Low level output voltage	Configured as an open-drain output, $I_{OL} = 2mA$ , $1.3V \leq VLDO1 \leq 1.8V$			0.6	V
$I_{(out)lkG}$	Output leakage current	Configured as an open-drain output, GPO connected to VLDO1		0.01	0.1	$\mu A$
<b>SCL, SDA</b>						
$V_{IH}$	High level input voltage on SCL, SDA		1.2		$V_{CC}$	V
$V_{IL}$	Low level input voltage on SCL, SDA		0		0.4	V
$I_{lkG}$	Pin leakage current on SCL, SDA (includes leakage current for the open-drain output)	Input at $V_{IL}$ or $V_{IH}$			100	nA
$V_{OL}$	Low level output voltage on SDA	For $I_{OL} = 1mA$			0.25	V
<b>UNDERVOLTAGE LOCKOUT (UVLO), SENSED AT PIN AVCC</b>						
UVLO	Internal undervoltage lockout threshold	$AV_{CC}$ rising	3.4	3.6	3.7	V
	Internal undervoltage lockout threshold hysteresis	$AV_{CC}$ falling		130		mV
<b>CLOCK GENERATOR</b>						
$f_{osc}$	Frequency of external crystal			24		MHz
$f_{CLKOUT}$	Frequency on pin CLKOUT	For OSC_FREQ[1,0] = 00		24		MHz
		For OSC_FREQ[1,0] = 01		12		
		For OSC_FREQ[1,0] = 10		6		
		For OSC_FREQ[1,0] = 11		3		
	Period jitter; rms	Measured period compared to the Average Period of 10,000 randomly selected cycles			600	ps
	Peak period to period jitter	Measured period compared to the Average Period of 10,000 randomly selected cycles			600	ps
	Duty cycle of CLKout		40%	50%	60%	
	Rise time / fall time for clock output	10% to 90% of output voltage, $1.3V \leq VLDO1 \leq 3.3V$			10	ns

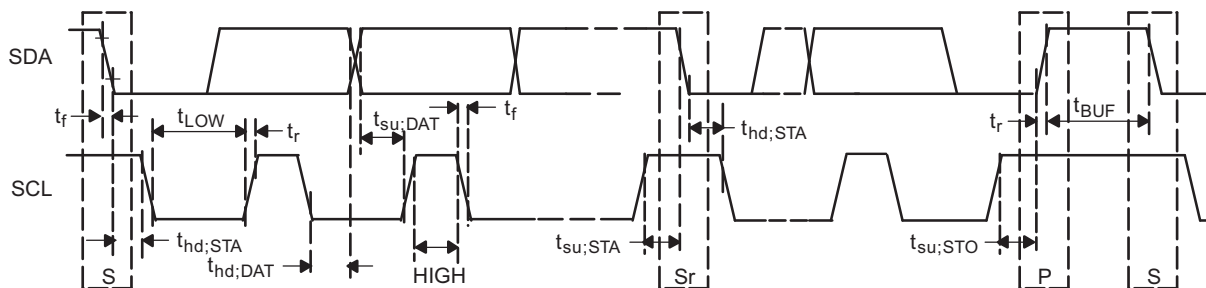
**Electrical Characteristics (continued)**

Unless otherwise noted:  $V_{CC} = AV_{CC} = 5V$ ,  $C_{VCC} = 1\mu F$ ;  $C_{OUTLDOx} = 2.2\mu F$ ,  $T_A = -40^{\circ}C$  to  $85^{\circ}C$ 

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
	Load capacitance	Defines the maximum capacitance that can be driven by the CLKOUT buffer and still meet the specified rise/fall times			15	pF
	Output impedance			50		$\Omega$
$V_{OH}$	High level output voltage	Internally connected to $V_{LDO1} \geq 1.8V$ : for $C_{OUT} = 15pF$ , $I_{OH} = 1mA$	1.6	$V_{LDO1} - 0.2V$	$V_{LDO1}$	V
$V_{OL}$	Low level output voltage	For $C_{OUT} = 15pF$ , $I_{OL} = 1mA$		0.2	0.3	V
$t_{start}$	Oscillator start-up time	Time from CLKout_EN=1 to CLKout active for the NXTBD-24.000M crystal, not tested in production but based on simulations			10	ms
<b>THERMAL PROTECTION</b>						
$T_{SD}$	Thermal shutdown	Increasing junction temperature		150		$^{\circ}C$
	Thermal shutdown hysteresis	Decreasing junction temperature		30		$^{\circ}C$
<b>VLDO1, VLDO2 LOW DROPOUT REGULATORS</b>						
$V_{CC}$	Input voltage range for LDO1 and LDO2		3.7		6	V
$V_{LDO1}$	LDO1 output voltage	See LDO1_CTRL Register definition for all available voltage settings.	0.8	1.8	3.3	V
$V_{LDO2}$	LDO2 output voltage	See LDO2_CTRL Register definition for all available voltage settings.	0.8	1.2	3.3	V
$I_O$	Output current for LDO1 and LDO2				100	mA
$I_{SC}$	LDO1 and LDO2 short circuit current limit	$V_{LDOx} = GND$	110		220	mA
	Dropout voltage at LDO1 and LDO2	$I_O = 75mA$ ; $V_{CC} \geq 3.7V$			700	mV
	Output voltage accuracy for LDO1 and LDO2	$V_{CC} = VLDO + 0.6V$ (min 3.7V) to 6V, $I_O = 2mA$ through 75mA, $T = 0^{\circ}C$ to $85^{\circ}C$	-1.5%		1.5%	
	Load Transient	$V_{CC} = AV_{CC} = 5V$ , $I_{O(LDOx)} = 0A$ to 75mA in 1us			10%	
PSRR	Power supply rejection ratio	$f = 10kHz$ , $C_{OUT} \geq 2.2\mu F$ , $V_{INLDOx} = 5V$ , $V_{OUT} = 1.8V$ , $I_{OUT} = 75mA$ ,		56		dB
	Output voltage rms noise	Voltage ripple and noise from 10kHz to 5MHz; Normal mode			4	mV
$t_{Ramp}$	$V_{OUT}$ ramp time	Time to ramp from 5% to 95% of $V_{OUT}$	24	50	200	$\mu s$
$R_{DIS}$	Internal discharge resistor at VLDO1 and VLDO2	$V_{IN} < UVLO$	200	400	550	$\Omega$
<b>MINIMUM ON TIME</b>						
	Minimum on time range		0		11	s
	Minimum on time accuracy	Accuracy based on the Minimum On Time Setting (1 LSB = 44ms)	-1		1	LSB
<b>LED CURRENT SINK</b>						
$I_{LED}$	Isink current (LED current for 99.9% duty cycle)			10		mA
	Minimum voltage drop from ISINK to GND needed for proper regulation	At $ISINK = 10mA$	0.3			V
	ISINK accuracy	$ISINK = 10mA$ , Duty Cycle set to 99.9%	-10%		5%	V
	PWM frequency settings	For PWM_FREQ[1,0] = 00		23.5		kHz
		For PWM_FREQ[1,0] = 01		11.7		
		For PWM_FREQ[1,0] = 10		5.8		
		For PWM_FREQ[1,0] = 11		2.9		
	PWM duty cycle range	Limited by ISINK rise / fall time for PWM_FREQ[1:0] other than 2'b11 setting	0%		99.9%	
	ISINK rise / fall time	$V_{(ISINK)} \geq 0.6V$ for $2mA \leq ISINK \leq 30mA$		400		ns

## 6.6 Timing Requirements

		MIN	MAX	UNIT
$f_{MAX}$	Clock frequency		400	kHz
$t_{(HIGH)}$	Clock high time	600		ns
$t_{(LOW)}$	Clock low time	1300		ns
$t_r$	DATA and CLK rise time		300	ns
$t_f$	DATA and CLK fall time		300	ns
$t_{hd;STA}$	Hold time (repeated) START condition (after this period the first clock pulse is generated)	600		ns
$t_{su;STA}$	Setup time for repeated START condition	600		ns
$t_{hd;DAT}$	Data input hold time	10		ns
$t_{su;DAT}$	Data input setup time	100		ns
$t_{su;STO}$	STOP condition setup time	600		ns
$t_{BUF}$	Bus free time	1300		ns
CI	load capacitance on SDA and SCL (with a 730 $\Omega$ or smaller pull-up resistor on SDA and SCL pulled up to 1.8V)		400	pF



**Figure 1. Serial I/f Timing Diagram**



## 6.7 Typical Characteristics

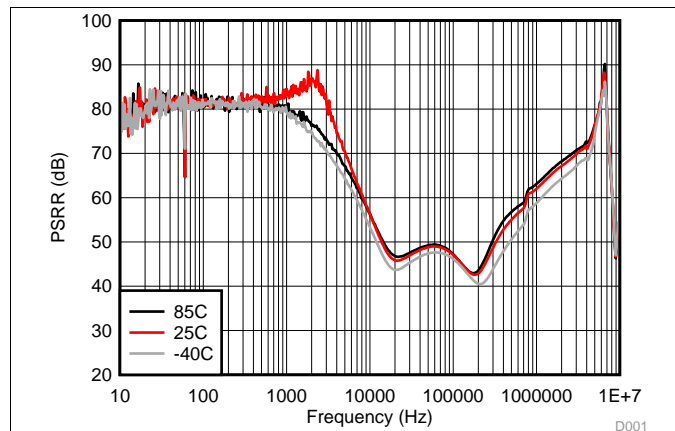


Figure 2. Power Supply Rejection Ratio (PSRR) for LDO1 at 1mA

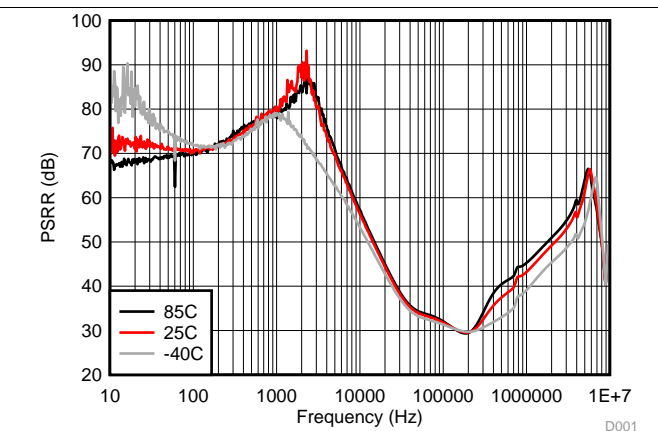


Figure 3. Power Supply Rejection Ratio (PSRR) for LDO1 at 75mA

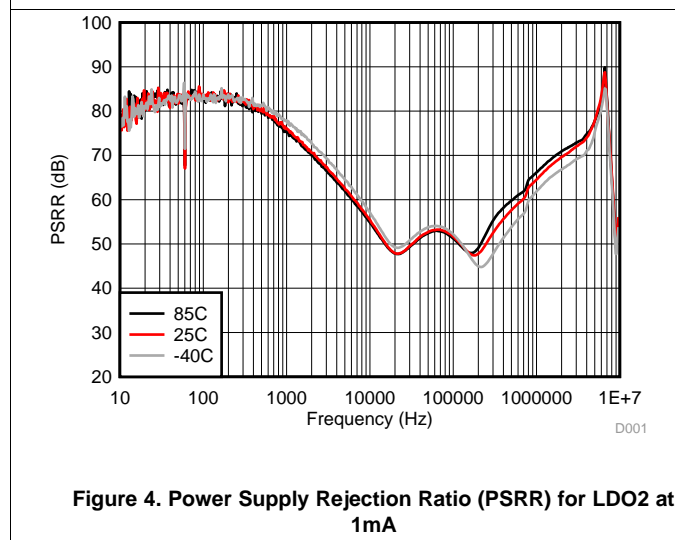


Figure 4. Power Supply Rejection Ratio (PSRR) for LDO2 at 1mA

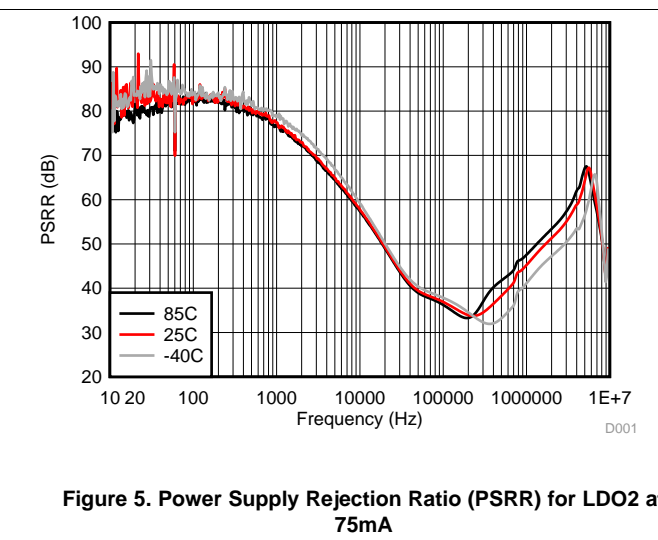


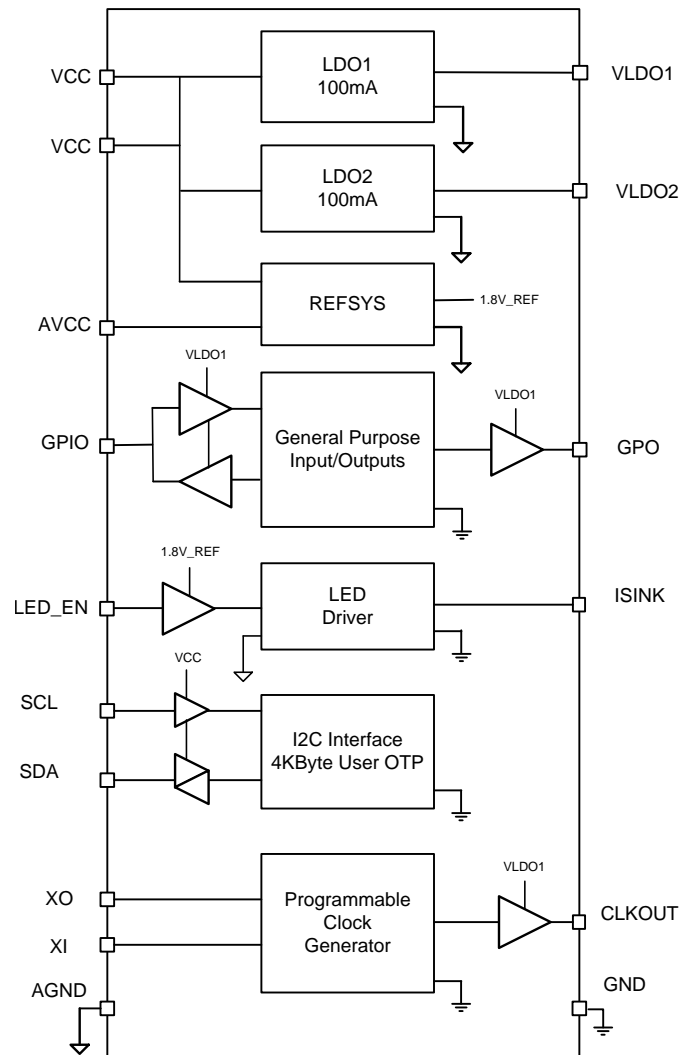
Figure 5. Power Supply Rejection Ratio (PSRR) for LDO2 at 75mA

## 7 Detailed Description

### 7.1 Overview

The TPS657095 integrates two LDOs, a PWM-dimmable current sink for driving an LED, one GPIO for controlling an external device and one GPO for controlling an embedded camera module.

### 7.2 Functional Block Diagram



### 7.3 Feature Description

#### 7.3.1 State Diagram

The state diagram below details the basic operation of this device.

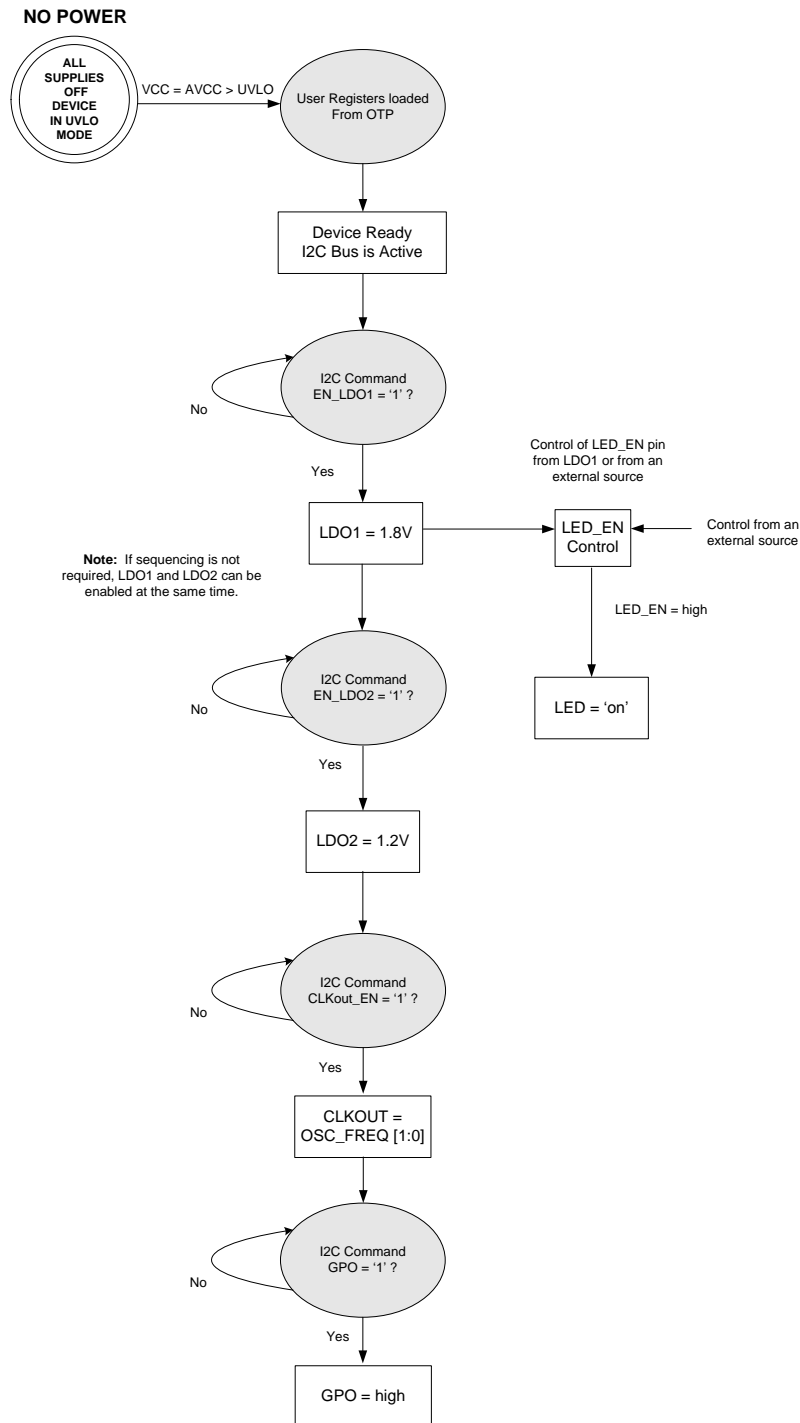
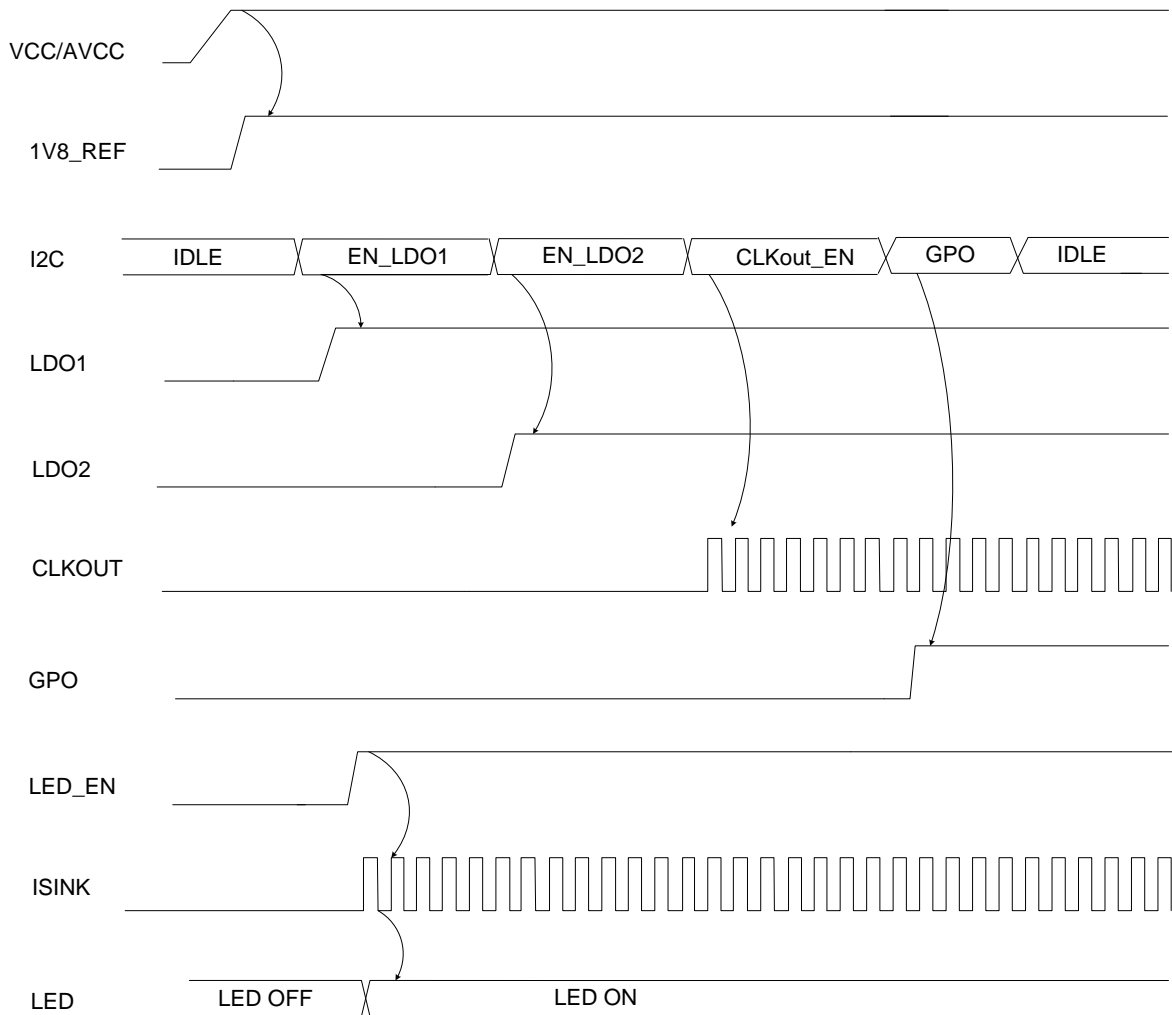


Figure 6. State Diagram

**Feature Description (continued)**
**7.3.2 Power-up Timing**

The timing diagram below details the state of the input signals and output voltages in a power-up event.



**Figure 7. Power-up Timing**

## Feature Description (continued)

### 7.3.3 GPO

The TPS657095 has one general purpose output (GPO) that can be used to control a camera image sensor. Bit 0 of the GPIO\_CTRL Register can be used to set the output level and bit 1 of the GPIO\_CTRL Register can be used to define whether the output is an open-drain or push-pull output. Internally, the GPO output buffer is connected to LDO1. Therefore, LDO1 has to be enabled in order for the GPO output to operate. In the open-drain configuration, the external pull-up resistor should be pulled up to a voltage that is equal to or less than VCC at all times. Connecting the pull-up resistor to a voltage source that is greater than VCC or present whenever VCC is not present may cause an unwanted leakage path.

### 7.3.4 GPIO

The TPS657095 has one general purpose input/output (GPIO) that can be used to control an external device when configured as an output. When configured as an input, the GPIO pin serves as a dedicated LDO2 enable. This discrete pin is 'ORed' with the software LDO2 enable. The functionality is shown in the following table.

**Table 1. LDO2 Output Control**

GPIO (configured as an input)	EN_LDO2 (bit 1 of the LDO_CTRL REGISTER)	LDO2 OUTPUT
0	0	Off
0	1	On
1	0	On
1	1	On

The GPIO\_CTRL register contains the bits used to configure this GPIO. Bit 3 of the GPIO\_CTRL Register can be used to set the output level, bit 4 can be used to configure the GPIO as an input or an output, and bit 5 of the GPIO\_CTRL Register can be used to define whether the output is an open-drain or push-pull output. Internally, the GPIO output buffer is connected to LDO1. Therefore, LDO1 has to be enabled in order for the GPIO to operate. In the open-drain configuration, the external pull-up resistor should be pulled up to a voltage that is equal to or less than VCC at all times. Connecting the pull-up resistor to a voltage source that is greater than VCC or present whenever VCC is not present may cause an unwanted leakage path.

### 7.3.5 LED\_EN

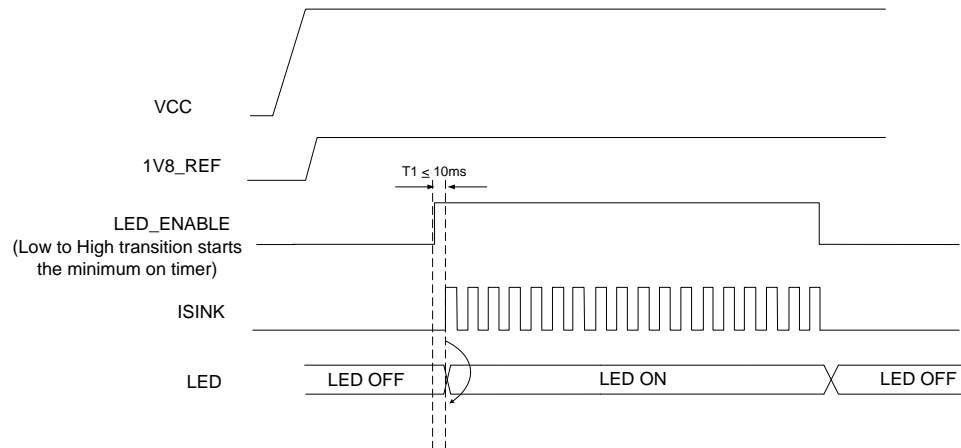
The TPS657095 has a pin, LED\_EN, which is used to control a privacy LED. The privacy LED can only be turned on or off using the LED\_EN pin. No other means to control the privacy LED exists in this device. Operation of the LED\_EN pin as it relates to minimum on time is shown in the Minimum-On-Time feature section of this document. The LED driver circuit of this device is internally biased by an internal 1.8V reference which is automatically powered once a valid voltage is present on the VCC/AVCC pins of this device. The input leakage current specified in the Electrical Characteristics section of this datasheet will not be exceeded even if a logic high voltage is applied to this pin while VCC/AVCC are not present.

### 7.3.6 Minimum-On-Time Feature

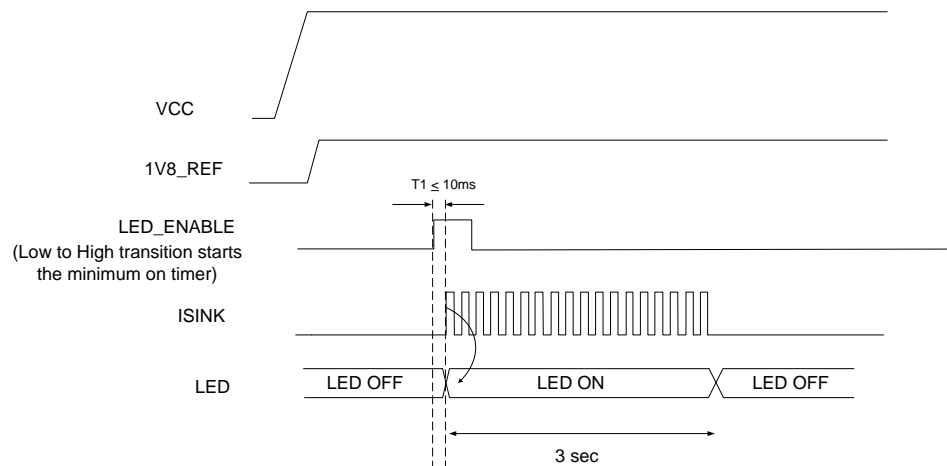
In order to ensure proper operation of a privacy LED, the TPS657095 device incorporates a Minimum-On-Time feature. The Minimum-On-Time for this device is programmed at the factory to a specified value which is shown in the MIN\_ON\_TIME\_THR Register. The user programmable Minimum-On-Time Register can be used to set a minimum on time for the LED. .

Once the Minimum-On-Time Register is loaded with a value and the internal PWM is enabled, the Minimum-On-Time timer will count to the value loaded. Writing a new value to the Minimum-On-Time Register prior to the timer expire will only take effect after the timer expires and the internal PWM is re-enabled.

Case #1:  
LED\_ENABLE is in the active state for a time much greater than the 'MIN\_ON\_TIME' register settings



Case #2:  
LED\_ENABLE is in the active state for a time less than the 'MIN\_ON\_TIME' register setting.  
(MIN\_ON\_TIME register set to 3 sec)



Case #3:  
LED\_ENABLE is in the active state for a time less than the 'MIN\_ON\_TIME' register setting  
(MIN\_ON\_TIME register set to 3.507 sec)

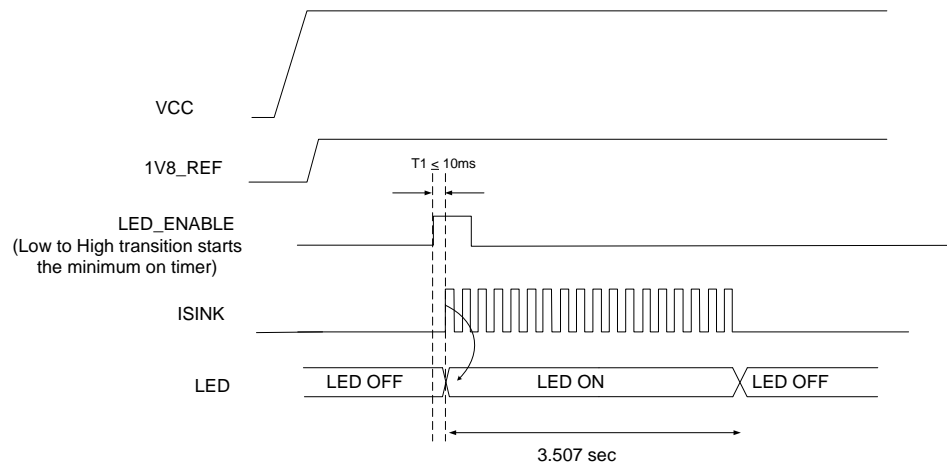


Figure 8. Minimum-On-Time Timing Diagrams

### 7.3.7 PWM Dimming

LED\_EN serves as the enable for the internal PWM.

- LED\_EN = 0: LED is OFF
- LED\_EN = 1: LED is ON / internal PWM is enabled

Since the crystal oscillator is needed for the internal PWM dimming, it is automatically enabled based on the status of the LED\_EN pin and on the CLKout\_EN register bit.

CLKout_EN	LED_EN	ISINK	CRYSTAL OSCILLATOR ENABLED	CLKout
0	0	OFF	OFF	OFF
0	1	ON - internal PWM	ON	OFF
1	0	OFF	ON	ON
1	1	ON - internal PWM	ON	ON

### 7.3.8 Crystal Oscillator and CLKOUT

The crystal oscillator is used to provide a clock signal to the camera image sensor via the CLKOUT pin. It is also used to control the internal PWM for dimming the LED and as the clock for the Minimum-On-Time counter. The crystal oscillator is enabled by either the CLKout\_EN bit in the PWM\_OSC\_CNTRL register or by driving the LED\_EN pin to a high state. Since the Minimum-On-Time counter is started when the LED\_EN input is driven to a high state, the crystal oscillator will remain on if the LED\_EN pin is driven to a low state and the Minimum-On-Time counter has yet to time out.

The CLKOUT buffer is internally supplied by LDO1, hence LDO1 needs to be enabled for proper functionality of the clock output. The CLKOUT buffer is enabled only when bit 2 of the PWM\_OSC\_CNTRL Register is set to a logic one. If bit 2 of the PWM\_OSC\_CNTRL register is set to a logic one while LDO1 is disabled, the crystal oscillator will run but the clock output will not be present on the CLKOUT pin. The OSC\_FREQ[1:0] bits in the PWM\_OSC\_CNTRL Register should be set prior to enabling the CLKOUT buffer.

In addition, the crystal oscillator is driving the internal charge pump that generates the programming voltage for the 4kByte OTP memory. For programming the OTP, the oscillator has to be enabled by setting CLKout\_EN to a logic '1' at least 10ms before the OTP is written to allow the crystal to stabilize.

The oscillator circuit used does not require external components other than the crystal itself on pins XI and XO. Internally, the oscillator circuit contains two 16pF capacitors connected from XI to GND and from XO to GND. It is designed for an equivalent series resistance of the crystal to be less than 100Ω. Therefore, a crystal must be used with a series resistance of less than this value and no other resistors in series or in parallel to the crystal must be added.

The signal on CLKOUT is delayed from the CLKout\_EN bit enabling the output buffer until the oscillator is stable. Once it has stabilized, an additional internal wait time of 131072 clk cycles x 1/24MHz has been added internally to the design before the output is set active. Given the typical start-up time of the crystal oscillator, it is safe to assume the total start-up time which depends on the crystal used including the 131072 cycles of clk delay is less than 10ms.

**Table 2. Tested Crystals**

TYPE	NOMINAL FREQUENCY	LOAD CAPACITANCE	EQUIVALENT SERIES RESISTANCE	SUPPLIER
8Q-24.000MEEV-T	24MHz	8pF (16pF on each pin)	100Ω maximum	TXC

### 7.3.9 LDOs

The low dropout voltage regulators are designed to operate with low value ceramic input and output capacitors. Both LDOs contain a current limit feature which is used at start up to control the voltage ramp time.

LDO1 is enabled by bit 0 of the LDO\_CTRL register. LDO2 can be enabled by either bit 1 of the LDO\_CTRL register or by the GPIO if configured as an input. Since the input buffer for the GPIO is powered by LDO1, LDO1 must be enabled before the GPIO pin can be used to enable LDO1. In the case of a thermal event, the register enable bits will be cleared with no auto-re-start feature so as to allow the application software to control the power sequencing of the LDOs.

### 7.3.10 Undervoltage Lockout

The undervoltage lockout circuit prevents the device from malfunctioning at low input voltages and from excessive discharge of the battery. It disables the complete device at low input voltages.

The supply voltage to the TPS657095 is internally sensed at pin AVCC. When the voltage at AVCC exceeds the UVLO limit, the internal enable signals turns HIGH and allows the device to operate. When the supply voltage drops below the UVLO limit, TPS657095 is forced OFF, all functions are disabled and the LDO output voltage discharge circuitry is forced ON to ramp down the output voltage. However, if the input voltage drops below 2V, the discharge circuit becomes inactive.

### 7.3.11 Power Up/Power Down Default States

The GPO, GPIO and CLKOUT pins contain internal buffers powered by LDO1. The following table shows their state during a power up (UVLO Rising) and power down (UVLO Falling) event.

**Table 3. Power Up/Power Down Events**

CIRCUIT	EVENT			
	VCC > UVLO, LDO1 turn-off	VCC rising > UVLO, LDO1 in an 'off' state	VCC > UVLO, LDO1 turn-on	VCC falling < UVLO, LDO1 in an 'off' state
GPO	Off <sup>1</sup>	Off <sup>1</sup>	Push-Pull, Low Level	Off <sup>1</sup>
GPIO	Off <sup>1,2</sup>	Off <sup>1,2</sup>	Input <sup>3</sup>	Off <sup>1</sup>
Register Bits	no change	OTP Load State	no change	Reset State
CLKOUT	Off <sup>1</sup>	Off <sup>1</sup>	Low (CLKOUT_EN = low)	Off <sup>1</sup>

Notes:

1. Output is 'off' as a result of no power supply. The output follows LDO1 to within a diode drop.
2. The GPIO\_STATE bit (bit 3 in the GPIO\_CTRL register) is forced to a logic low.
3. The default setting is configured as an input. This can be modified by using the GPIO\_CTRL register.

### 7.3.12 Output Voltage Discharge for LDO1 and LDO2

The LDOs contain an output capacitor discharge feature which makes sure that the capacitor is discharged to GND when the supply voltage drops below the undervoltage lockout threshold. The discharge function is enabled when voltage is applied at AVCC starting at about 2.1V until the LDOs are enabled.

### 7.3.13 Power-Good Status Bits for LDO1 and LDO2

Bits PGOOD\_LDO1 and PGOOD\_LDO2 in register LDO\_CTRL are driven by a comparator inside the LDOs to indicate when the output voltage is in regulation. The Bits are set 'high' when the LDO is in regulation. When the LDO is enabled but the voltage is not above the power-good threshold, the bit is set to a 'low' state. The bit is also set to a 'low' state if the LDO is disabled.

### 7.3.14 Short-Circuit Protection

All outputs are short circuit protected with a maximum output current as defined in the electrical specifications.

### 7.3.15 Thermal Shutdown

As soon as the junction temperature,  $T_J$ , exceeds 150°C (typically) for any of the LDOs, the LDO will go into thermal shutdown. In this case, the LDOs are turned-off. After the temperature has fallen below the threshold, the LDO remains off until it is enabled again by the I2C interface. There is no automatic power-on feature once the thermal event is past.



### 7.3.16 LED Driver

The TPS657095 contains a LED driver for a current of up to 30mA. ISINK is an open drain current sink that regulates a current in a LED. The anode of the LED needs to be tied to a positive supply voltage e.g.,  $V_{CC}$  or any other voltage within the limits of the electrical spec of TPS657095, depending on the forward voltage of the LED. The cathode of the LED is connected to ISINK which sets a constant current to GND. ISINK is regulated internally based on the default current set internally. If the LED\_EN pin is pulled LOW, the LED driver is disabled and its output ISINK is high resistive. If LED\_EN is HIGH, the current sink regulates to the current defined by the setting in the ISINK\_CURRENT Register.

The internal PWM generator allows for internal dimming with a frequency of 3kHz, 6kHz, 12kHz or 24kHz. A 10Bit duty cycle register allows to set the duty cycle in a range from 0% to 99.9% using 8Bits PWM resolution and another 2Bits of dithering.

A signal applied at the LED\_EN pin is used to synchronously enable and disable the internal PWM signal.

### 7.3.17 4kByte OTP Memory

The TPS657095 contains 4kBytes of one-time-programmable (OTP) memory to store user data. The memory has a linear address range from 0x0000 to 0x0FFF and uses two Byte addressing as described in the serial interface description. Reading beyond the specified linear address range will result in reading all zeros. Writes to an address space beyond the specified linear address range are inhibited.

The 4kByte OTP memory requires a programming voltage higher than 5V. The program voltage is generated internally by a charge pump which uses the VCC voltage as its input. During programming, Vcc has to be kept at 5V +/-5% (a voltage of 5.25V is recommended) and the internal oscillator has to be enabled 10ms before programming to allow the 24MHz crystal to stabilize. The 24MHz clock is needed for the internal charge pump to generate the programming voltage from Vcc.

As an added security measure, programming the 4kByte OTP memory requires a two byte sequential password to be written to in the PMU register space at address 0x0F. The two bytes must be written back to back with no restriction on the delay between the writes. Any data written at address 0x0F that does not match the password and sequence will disable the ability to program the 4kByte OTP memory.

#### 7.3.17.1 Programming the 4KByte OTP Memory

1. Apply 5V +/-5% to the VCC and AVCC pins.
2. Enable the internal oscillator by driving the LED\_EN pin to a high state or setting the CLKout\_EN bit to a '1'.
3. Wait at least 10ms for the crystal to stabilize.
3. Using the PMU register I2C address, write the password to the 4K\_OTP\_PASSWORD register.
4. Using the 4kByte OTP memory I2C address, write the desired value to a specific address using the protocol shown in Figure 6.
5. Exit the programming of the 4KByte OTP memory by over writing the 4K\_OTP\_PASSWORD register with an incorrect password or by removing power to the device.

## 7.4 Device Functional Modes

### 7.4.1 Shutdown Mode

The TPS657095 is in a 'Shutdown' mode if the voltage on the AVCC pin is below 1.8V. In this mode, the device will not respond to I2C commands nor will the LED\_EN pin be operational.

### 7.4.2 Operational Mode

The TPS657095 enters an 'Operational' mode mode once a voltage greater than the UVLO limit is present on both the VCC and AVCC pins. In this mode, the I2C is active, the operation of the LED is controllable via the LED\_EN pin and the LDOs can be enabled.

## Device Functional Modes (continued)

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### NOTE

The voltage on the AVCC and VCC pins should not be left in a state between the Shutdown Mode voltage and the Operational Mode voltage. Keeping the input voltage to the device in this indeterminate state will result in unwanted quiescent current consumption.

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## 7.5 Programming

### 7.5.1 Serial Interface

The serial interface is compatible with the standard and fast mode I<sup>2</sup>C specifications, allowing transfers at up to 400kHz. The interface adds flexibility to the power supply solution, enabling most functions to be programmed to new values depending on the instantaneous application requirements and charger status to be monitored. Register contents remain intact as long as VCC remains above the UVLO threshold. The I<sup>2</sup>C interface is running from an internal oscillator that is automatically enabled when there is an access to the interface. Additional features supported by the I<sup>2</sup>C compatible interface are:

- multi-byte read/write capability
- clock stretching; specifically needed during OTP write

The 7bit device address for TPS657095 is:

- "100 1000" for the PMU user registers
- "101 1000" for the 4kByte OTP memory

For the PMU, at address "100 1000", the device address is followed by the 1Byte register address and 1Byte data (for a write instruction)

For the 4kByte OTP memory, at address "101 1000", the device address is followed by the 1Byte register address [7:0] followed by the second address Byte [15:8] and 1Byte data (for a write instruction) giving a 4kByte linear address range for the memory. Please note that the supply voltage range at pins VCC and AVCC during programming (writing) of the OTP memory is limited to 5V  $\pm$ 5%.

Attempting to read data from register addresses not listed in this section will result in 00h being read out.

For normal data transfer, DATA is allowed to change only when CLK is low. Changes when CLK is high are reserved for indicating the start and stop conditions. During data transfer, the data line must remain stable whenever the clock line is high. There is one clock pulse per bit of data. Each data transfer is initiated with a start condition and terminated with a stop condition. When addressed, the TPS657095 generates an acknowledge bit after the reception of each byte. The master device (microprocessor) must generate an extra clock pulse that is associated with the acknowledge bit. The TPS657095 must pull down the DATA line during the acknowledge clock pulse so that the DATA line is a stable low during the high period of the acknowledge clock pulse. The DATA line is a stable low during the high period of the acknowledge-related clock pulse. Setup and hold times must be taken into account. During read operations, a master must signal the end of data to the slave by not generating an acknowledge bit on the last byte that was clocked out of the slave. In this case, the slave device TPS657095 must leave the data line high to enable the master to generate the stop condition.

The interface is reset by the internal UVLO signal of TPS657095 or by a STOP condition. If the SCL and SDA signal is not stable at the time the UVLO threshold on pin Vcc is exceeded, the first communication may not be acknowledged and will have to be re-transmitted after a STOP condition.

Upon the application of power on the VCC/AVCC pins, the internal I2C buffers may sequence up in a manner that produces a false START. If a false START is detected, an internal synchronization clock will be enabled until a STOP condition is received. During the time that the internal synchronization clock is active, the device will consume an additional 120uA of current.

Programming (continued)

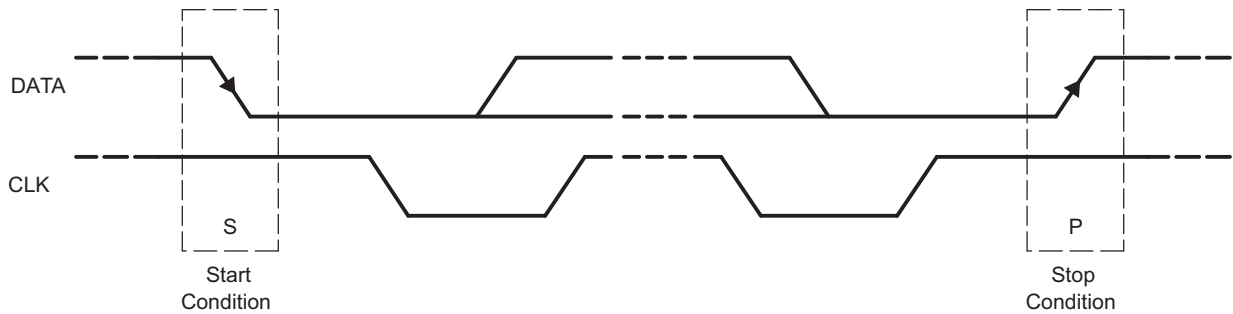
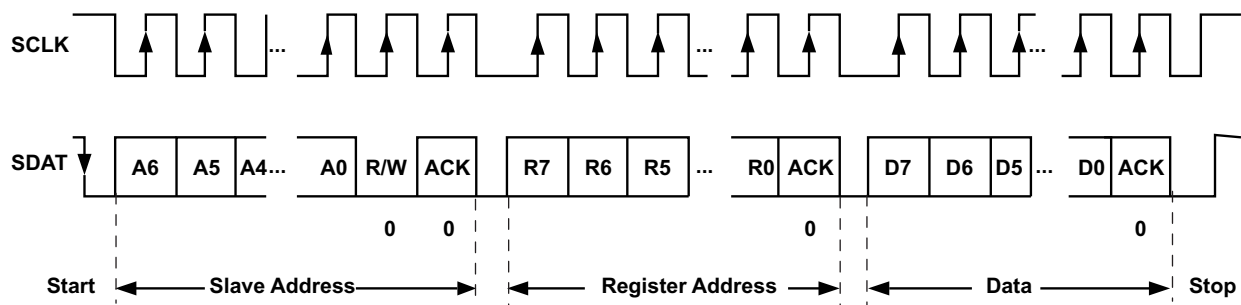
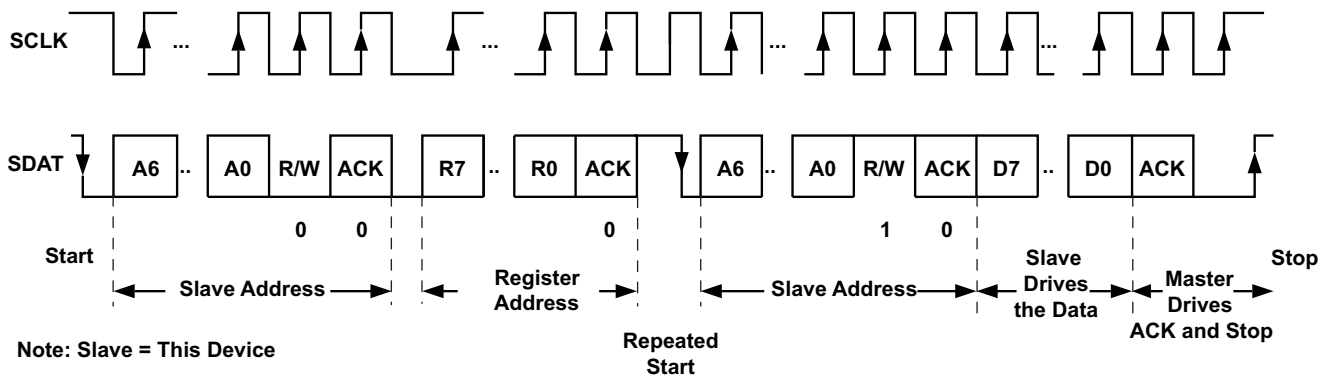


Figure 9. START and STOP Conditions



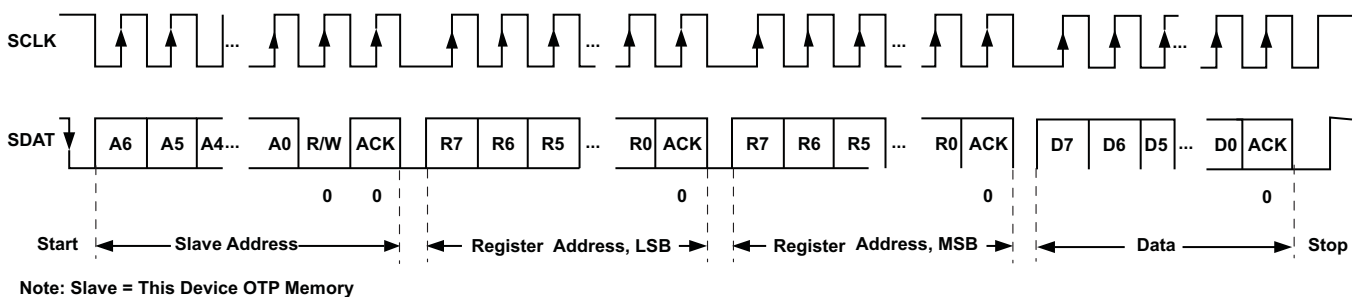
Note: Slave = This Device

Figure 10. Serial Interface WRITE to TPS657095 User Registers



Note: Slave = This Device

Figure 11. Serial Interface READ from TPS657095 User Registers



Note: Slave = This Device OTP Memory

Figure 12. Serial Interface WRITE to TPS657095 OTP Memory

Programming (continued)

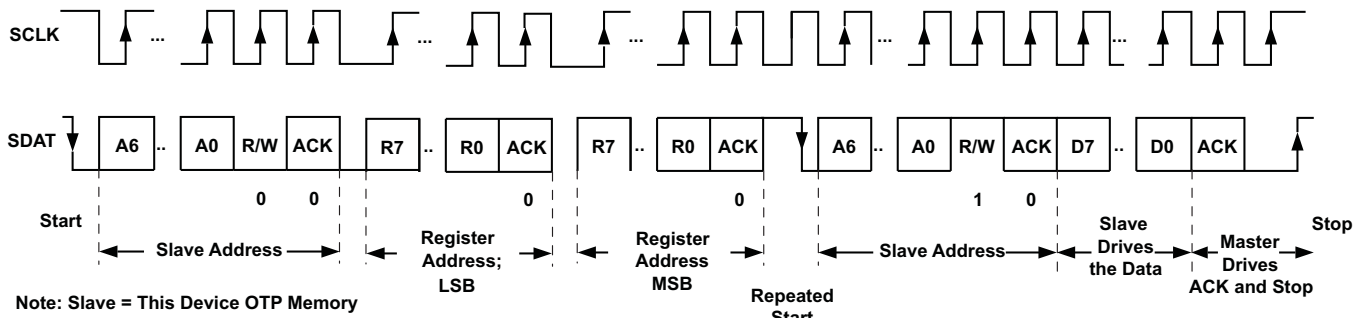


Figure 13. Serial Interface READ from TPS657095 OTP Memory

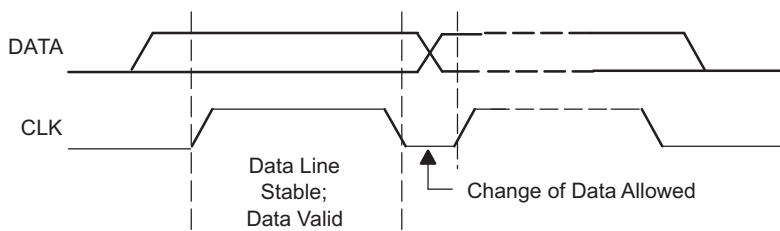


Figure 14. Bit Transfer on the Serial Interface

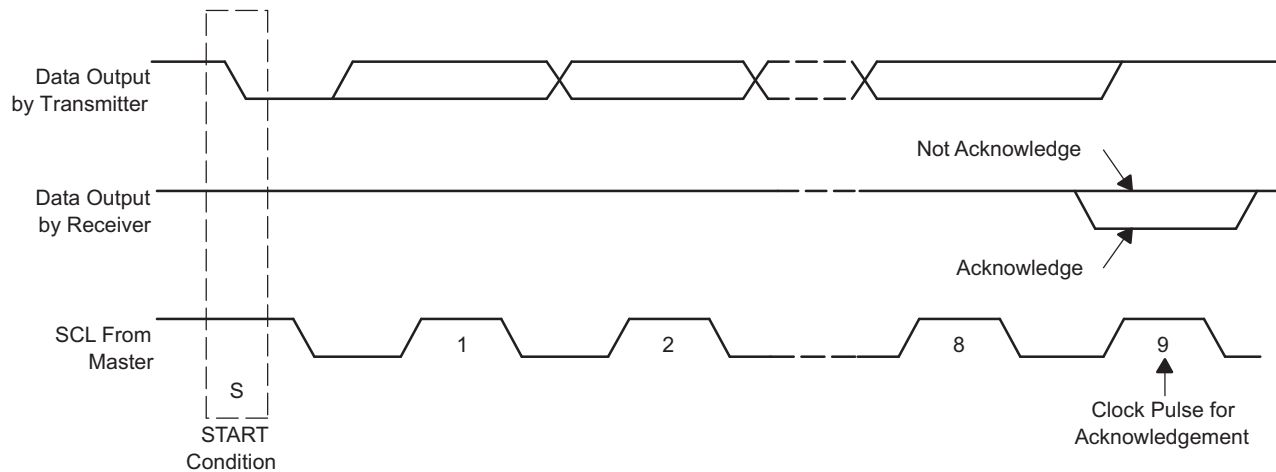


Figure 15. Acknowledge on the I<sup>2</sup>C Bus

Programming (continued)

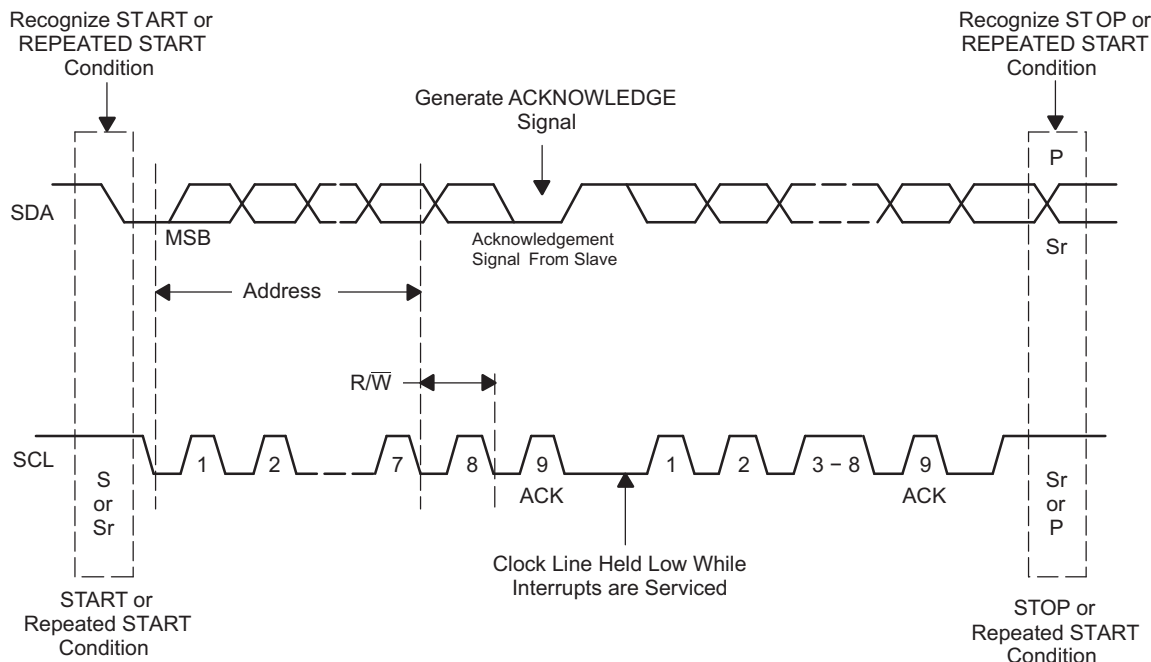


Figure 16. Bus Protocol

## 7.6 Register Map

### 7.6.1 DEV\_AND\_REV\_ID Register Address: 00h

**Figure 17. DEV\_AND\_REV\_ID Register**

DEV_AND_REV_ID	B7	B6	B5	B4	B3	B2	B1	BO
Bit name and function	DEV_ID[3]	DEV_ID[2]	DEV_ID[1]	DEV_ID[0]	REV_ID[3]	REV_ID[2]	REV_ID[1]	REV_ID[0]
Default	0	1	0	1	0	1	0	0
Default set by:	OTP	OTP	OTP	OTP	OTP	OTP	OTP	OTP
Default value loaded by:	UVLO	UVLO	UVLO	UVLO	UVLO	UVLO	UVLO	UVLO
Read/write	R	R	R	R	R	R	R	R

LEGEND: R/W = Read/Write; R = Read only; -n = value after reset

**Table 4. DEV\_AND\_REV\_ID Field Descriptions**

Bit	Field	Type	Reset	Description
Bit 7:4	DEV_ID[3:0]	R	0101	Device ID: TPS657095 = 0101
Bit 3:0	REV_ID[3:0]	R	0100	Die Revision ID: PG1.0 = 0100

### 7.6.2 OTP\_REV Register Address: 01h

**Figure 18. OTP\_REV Register Address: 01h Register**

OTP_REV	B7	B6	B5	B4	B3	B2	B1	BO
Bit name and function	RSVD	OTP_REV[6]	OTP_REV[5]	OTP_REV[4]	OTP_REV[3]	OTP_REV[2]	OTP_REV[1]	OTP_REV[0]
Default	0	1	0	0	0	0	0	0
Default set by:	OTP	OTP	OTP	OTP	OTP	OTP	OTP	OTP
Default value loaded by:	UVLO	UVLO	UVLO	UVLO	UVLO	UVLO	UVLO	UVLO
Read/write	R	R	R	R	R	R	R	R

LEGEND: R/W = Read/Write; R = Read only; -n = value after reset

**Table 5. OTP\_REV Register Address: 01h Register Field Descriptions**

Bit	Field	Type	Reset	Description
Bit 7	RSVD	R	0	
Bit 6:0	OTP_REV[6:0]	R	1000000	Reserved: 100_0000: Production PG1.0 programming

**7.6.3 GPIO\_CTRL Register Address: 02h**
**Figure 19. GPIO\_CTRL Register**

GPIO_CTRL	B7	B6	B5	B4	B3	B2	B1	B0
Bit name and function	SPARE	SPARE	GPIO_driver	GPIO_DIR	GPIO_STATE	SPARE	GPO_driver	GPO
Default	0	0	1	1	1	0	0	0
Default set by:	OTP	OTP	OTP	OTP	OTP	OTP	OTP	OTP
Default value loaded by:	UVLO	UVLO	UVLO	UVLO	UVLO	UVLO	UVLO	UVLO
Read/write	R	R	R/W	R/W	R/W	R	R/W	R/W

LEGEND: R/W = Read/Write; R = Read only; -n = value after reset

**Table 6. GPIO\_CTRL Register Field Descriptions**

Bit	Field	Type	Reset	Description
Bit 7:6	SPARE	R	00	
Bit 5	GPIO_driver	R/W	1	0 = GPIO is configured as push pull output; internally connected to LDO1 1 = GPIO is configured as open drain output
Bit 4	GPIO_DIR	R/W	1	0 = GPIO is configured as an input and used to enable LDO2 1 = GPIO is configured as an output
Bit 3	GPIO_STATE	R/W	1	0 = actively pulled low 1 = high impedance output if the GPIO_driver bit is configured as an open-drain output / internally pulled up to the LDO1 voltage setting if the GPIO_driver bit is configured as a push-pull output
Bit 2	SPARE	R	0	
Bit 1	GPO_driver	R/W	0	0 = GPO is configured as push pull output; internally connected to LDO1 1 = GPO is configured as open drain output
Bit 0	GPO	R/W	0	0 = actively pulled low 1 = high impedance output if the GPO_driver bit is configured as an open-drain output / internally pulled up to the LDO1 voltage setting if the GPO_driver bit is configured as a push-pull output

**7.6.4 PWM\_OSC\_CNTRL Register Address: 03h**
**Figure 20. PWM\_OSC\_CNTRL Register**

OSCILLATOR_CONTROL	B7	B6	B5	B4	B3	B2	B1	B0
Bit name and function	SPARE	SPARE	SPARE	PWM_FREQ[1]	PWM_FREQ[0]	CLKout_EN	OSC_FREQ[1]	OSC_FREQ[0]
Default	0	0	0	1	1	0	0	0
Default set by:	OTP	OTP	OTP	OTP	OTP	OTP	OTP	OTP
Default value loaded by:	UVLO	UVLO	UVLO	UVLO	UVLO	UVLO	UVLO	UVLO
Read/write	R	R	R	R/W	R/W	R/W	R/W	R/W

LEGEND: R/W = Read/Write; R = Read only; -n = value after reset

**Table 7. PWM\_OSC\_CNTRL Register Field Descriptions**

Bit	Field	Type	Reset	Description
Bit 7:5	SPARE	R	000	
Bit 4:3	PWM_FREQ[1:0]	R/W	11	Frequency divider for internally generated PWM signal: 00 : f(PWM) = 23.5KHz 01 : f(PWM) = 11.7KHz 10 : f(PWM) = 5.8KHz 11 : f(PWM) = 2.9KHz
Bit 2	CLKout_EN	R/W	0	0 = CLKOUT is disabled and the output is held LOW 1 = the crystal oscillator is forced ON; CLKOUT is enabled and is switching with the frequency defined by OSC_FREQ[1..0]; LDO1 needs to be enabled for CLKout being active Please note that the crystal oscillator itself is active once the Bit is set high, independently of the status of LDO1.
Bit 1:0	OSC_FREQ[1:0]	R/W	00	Frequency divider for CLKOUT generated from 24MHz crystal 00 : f(CLKOUT) = f(OSC) = 24MHz 01 : f(CLKOUT) = f(OSC) / 2 = 12MHz 10 : f(CLKOUT) = f(OSC) / 4 = 6MHz 11 : f(CLKOUT) = f(OSC) / 8 = 3MHz

**7.6.5 ISINK\_CURRENT Register Address: 04h**
**Figure 21. ISINK\_CURRENT Register**

ISINK_CURRENT	B7	B6	B5	B4	B3	B2	B1	B0
Bit name and function	SPARE	SPARE	SPARE	ISINK[4]	ISINK[3]	ISINK[2]	ISINK[1]	ISINK[0]
Default	0	0	0	0	1	0	0	0
Default set by:	OTP	OTP	OTP	OTP	OTP	OTP	OTP	OTP
Default value loaded by:	UVLO	UVLO	UVLO	UVLO	UVLO	UVLO	UVLO	UVLO
Read/write	R	R	R	R	R	R	R	R

LEGEND: R/W = Read/Write; R = Read only; -n = value after reset

**Table 8. ISINK\_CURRENT Register Field Descriptions**

Bit	Field	Type	Reset	Description
Bit 7:5	SPARE	R	000	
Bit 4:0	ISINK[4:0]	R	01000	ISINK dc current setting TPS657095: Factory programmed to 5'b01000 (10mA)



**7.6.6 LDO\_CTRL Register Address: 05h**
**Figure 22. LDO\_CTRL Register**

LDO_CTRL	B7	B6	B5	B4	B3	B2	B1	B0
Bit name and function	SPARE	SPARE	PGOOD_LDO2	PGOOD_LDO1	SPARE	SPARE	EN_LDO2	EN_LDO1
Default	0	0	-	-	0	0	0	0
Default set by:	OTP	OTP	OTP	OTP	OTP	OTP	OTP	OTP
Default value loaded by:	UVLO	UVLO	PGOOD of LDO2	PGOOD of LDO1	UVLO	UVLO	UVLO	UVLO
Read/write	R	R	R	R	R	R	R/W	R/W

LEGEND: R/W = Read/Write; R = Read only; -n = value after reset

**Table 9. LDO\_CTRL Register Field Descriptions**

Bit	Field	Type	Reset	Description
Bit 7:6	SPARE	R	00	
Bit 5	PGOOD LDO2	R	-	Power good status Bit for LDO2 0 = the output voltage of LDO2 is below the power good threshold or LDO2 is disabled; default value as LDO2 is disabled by default 1 = the output voltage of LDO2 is above the power good threshold
Bit 4	PGOOD LDO1	R	-	Power good status Bit for LDO1: 0 = the output voltage of LDO1 is below the power good threshold or LDO1 is disabled; default value as LDO1 is disabled by default 1 = the output voltage of LDO1 is above the power good threshold
Bit 3	NC:	R	0	
Bit 2	SPARE	R	0	
Bit 1	EN_LDO2	R/W	0	0 = LDO2 is disabled (Default: TPS657095) 1 = LDO2 is enabled
Bit 0	EN_LDO1	R/W	0	0 = LDO1 is disabled (Default: TPS657095) 1 = LDO1 is enabled

7.6.7 LDO1\_VCTRL Register Address: 06h

Figure 23. LDO1\_VCTRL Register

LDO1_VCTRL	B7	B6	B5	B4	B3	B2	B1	B0
Bit name and function	SPARE	SPARE	LDO1[5]	LDO1[4]	LDO1[3]	LDO1[2]	LDO1[1]	LDO1[0]
Default	0	0	1	0	0	1	0	0
Default set by:	OTP	OTP	OTP	OTP	OTP	OTP	OTP	OTP
Default value loaded by:	UVLO	UVLO	UVLO	UVLO	UVLO	UVLO	UVLO	UVLO
Read/write	R	R	R/W	R/W	R/W	R/W	R/W	R/W

LEGEND: R/W = Read/Write; R = Read only; -n = value after reset

Table 10. LDO1\_VCTRL Register Field Descriptions

Bit	Field	Type	Reset	Description
Bit 7:6	SPARE	R	00	
Bit 5:0	LDO1[5:0]	R/W	100100	Output voltage setting for LDO1 <sup>(1)(2)</sup>

- (1) A Voltage change during operation must not exceed 8% of the value set in the register for each I2C write access as this may trigger the internal power good comparator and will trigger the Reset of the device. This limitation is only for a voltage step to higher voltages. There is no limitation for programming lower voltages by I2C.
- (2) The output voltage setting cannot be changed if the LOCK\_BIT in the OTP\_REV\_LOCK\_BIT register is set to a logic '1'.

7.6.8 LDO2\_VCTRL Register Address: 07h

Figure 24. LDO2\_VCTRL Register

LDO2_VCTRL	B7	B6	B5	B4	B3	B2	B1	B0
Bit name and function	SPARE	SPARE	LDO2[5]	LDO2[4]	LDO2[3]	LDO2[2]	LDO2[1]	LDO2[0]
Default	0	0	0	1	0	0	0	0
Default set by:	OTP	OTP	OTP	OTP	OTP	OTP	OTP	OTP
Default value loaded by:	UVLO	UVLO	UVLO	UVLO	UVLO	UVLO	UVLO	UVLO
Read/write	R	R	R/W	R/W	R/W	R/W	R/W	R/W

LEGEND: R/W = Read/Write; R = Read only; -n = value after reset

Table 11. LDO2\_VCTRL Field Descriptions

Bit	Field	Type	Reset	Description
Bit 7:6	SPARE	R	00	
Bit 5:0	LDO2[5:0]	R/W	010000	Output voltage setting for LDO2 <sup>(1)(2)</sup>

- (1) A Voltage change during operation must not exceed 8% of the value set in the register for each I2C write access as this may trigger the internal power good comparator and will trigger the Reset of the device. This limitation is only for a voltage step to higher voltages. There is no limitation for programming lower voltages by I2C.
- (2) The output voltage setting cannot be changed if the LOCK\_BIT in the OTP\_REV\_LOCK\_BIT register is set to a logic '1'.

	OUTPUT VOLTAGE [V]	B5	B4	B3	B2	B1	B0
0	0.800	0	0	0	0	0	0
1	0.825	0	0	0	0	0	1
2	0.850	0	0	0	0	1	0
3	0.875	0	0	0	0	1	1
4	0.900	0	0	0	1	0	0
5	0.925	0	0	0	1	0	1

	OUTPUT VOLTAGE [V]	B5	B4	B3	B2	B1	B0
6	0.950	0	0	0	1	1	0
7	0.975	0	0	0	1	1	1
8	1.000	0	0	1	0	0	0
9	1.025	0	0	1	0	0	1
10	1.050	0	0	1	0	1	0
11	1.075	0	0	1	0	1	1
12	1.100	0	0	1	1	0	0
13	1.125	0	0	1	1	0	1
14	1.150	0	0	1	1	1	0
15	1.175	0	0	1	1	1	1
16	1.200	0	1	0	0	0	0
17	1.225	0	1	0	0	0	1
18	1.250	0	1	0	0	1	0
19	1.275	0	1	0	0	1	1
20	1.300	0	1	0	1	0	0
21	1.325	0	1	0	1	0	1
22	1.350	0	1	0	1	1	0
23	1.375	0	1	0	1	1	1
24	1.400	0	1	1	0	0	0
25	1.425	0	1	1	0	0	1
26	1.450	0	1	1	0	1	0
27	1.475	0	1	1	0	1	1
28	1.500	0	1	1	1	0	0
29	1.525	0	1	1	1	0	1
30	1.550	0	1	1	1	1	0
31	1.575	0	1	1	1	1	1
32	1.600	1	0	0	0	0	0
33	1.650	1	0	0	0	0	1
34	1.700	1	0	0	0	1	0
35	1.750	1	0	0	0	1	1
36	1.800	1	0	0	1	0	0
37	1.850	1	0	0	1	0	1
38	1.900	1	0	0	1	1	0
39	1.950	1	0	0	1	1	1
40	2.000	1	0	1	0	0	0
41	2.050	1	0	1	0	0	1
42	2.100	1	0	1	0	1	0
43	2.150	1	0	1	0	1	1
44	2.200	1	0	1	1	0	0
45	2.250	1	0	1	1	0	1
46	2.300	1	0	1	1	1	0
47	2.350	1	0	1	1	1	1
48	2.400	1	1	0	0	0	0
49	2.450	1	1	0	0	0	1
50	2.500	1	1	0	0	1	0
51	2.550	1	1	0	0	1	1
52	2.600	1	1	0	1	0	0
53	2.650	1	1	0	1	0	1
54	2.700	1	1	0	1	1	0

	OUTPUT VOLTAGE [V]	B5	B4	B3	B2	B1	B0
55	2.750	1	1	0	1	1	1
56	2.800	1	1	1	0	0	0
57	2.850	1	1	1	0	0	1
58	2.900	1	1	1	0	1	0
59	2.950	1	1	1	0	1	1
60	3.000	1	1	1	1	0	0
61	3.100	1	1	1	1	0	1
62	3.200	1	1	1	1	1	0
63	3.300	1	1	1	1	1	1

### 7.6.9 PWM\_DUTY\_THR\_L Register Address: 08h

**Figure 25. PWM\_DUTY\_THR\_L Register**

PWM_DUTY_THR_L	B7	B6	B5	B4	B3	B2	B1	B0
Bit name and function	PWM_DC_TH[7]	PWM_DC_TH[6]	PWM_DC_TH[5]	PWM_DC_TH[4]	PWM_DC_TH[3]	PWM_DC_TH[2]	PWM_DC_TH[1]	PWM_DC_TH[0]
Default	1	1	1	1	1	1	1	1
Default set by:	OTP	OTP	OTP	OTP	OTP	OTP	OTP	OTP
Default value loaded by:	UVLO	UVLO	UVLO	UVLO	UVLO	UVLO	UVLO	UVLO
Read/write	R	R	R	R	R	R	R	R

LEGEND: R/W = Read/Write; R = Read only; -n = value after reset

**Table 12. PWM\_DUTY\_THR\_L Register Field Descriptions**

Bit	Field	Type	Reset	Description
Bit 7:0	PWM_DC_TH[7:0]	R	11111111	Lower 8 bits of PWM duty cycle threshold for internally generated PWM on ISINK <sup>(1)</sup>

(1) The contents of the PWM\_DUTY\_THR\_L register is factory programmed and read only.

### 7.6.10 PWM\_DUTY\_THR\_H Register Address: 09h

**Figure 26. PWM\_DUTY\_THR\_H Register**

PWM_DUTY_THR_H	B7	B6	B5	B4	B3	B2	B1	B0
Bit name and function							PWM_DC_TH[9]	PWM_DC_TH[8]
Default	0	0	0	0	0	0	0	0
Default set by:	OTP	OTP	OTP	OTP	OTP	OTP	OTP	OTP
Default value loaded by:	UVLO	UVLO	UVLO	UVLO	UVLO	UVLO	UVLO	UVLO
Read/write	R	R	R	R	R	R	R	R

LEGEND: R/W = Read/Write; R = Read only; -n = value after reset

**Table 13. PWM\_DUTY\_THR\_H Register Field Descriptions**

Bit	Field	Type	Reset	Description
Bit 7:0	PWM_DC_TH[7:0]	R	00000000	Higher 2 Bits of PWM duty cycle threshold for internally generated PWM on ISINK
	PWM_DC_TH[9:0]	R	00000000	000h = 0% duty cycle 3FFh = 99.9% duty cycle
				Any attempt to write a lower value into PWM_DUTY than defined in PWM_DUTY_THR will be ignored. <sup>(1)</sup>

(1) The contents of the PWM\_DUTY\_THR\_H register is factory programmed and read only.

**7.6.11 MIN\_ON\_TIME\_THR Register Address: 0Ah**
**Figure 27. MIN\_ON\_TIME\_THR Register**

MIN_ON_TIME_THR	B7	B6	B5	B4	B3	B2	B1	BO
Bit name and function	MOT_THR[7]	MOT_THR[6]	MOT_THR[5]	MOT_THR[4]	MOT_THR[3]	MOT_THR[2]	MOT_THR[1]	MOT_THR[0]
Default	0	0	0	0	0	0	0	0
Default set by:	OTP	OTP	OTP	OTP	OTP	OTP	OTP	OTP
Default value loaded by:	UVLO	UVLO	UVLO	UVLO	UVLO	UVLO	UVLO	UVLO
Read/write	R	R	R	R	R	R	R	R

LEGEND: R/W = Read/Write; R = Read only; -n = value after reset

**Table 14. MIN\_ON\_TIME\_THR Register Field Descriptions**

Bit	Field	Type	Reset	Description
Bit 7:0	MOT_THR[7:0]	R	00000000	Minimum On Time Threshold Setting 0x00: 0 seconds

**7.6.12 PWM\_DUTY\_L Register Address: 0Bh**
**Figure 28. PWM\_DUTY\_L Register**

PWM_DUTY_L	B7	B6	B5	B4	B3	B2	B1	BO
Bit name and function	PWM_DC[7]	PWM_DC[6]	PWM_DC[5]	PWM_DC[4]	PWM_DC[3]	PWM_DC[2]	PWM_DC[1]	PWM_DC[0]; LSB
Default	see Note1	see Note1	see Note1	see Note1	see Note1	see Note1	see Note1	see Note1
Default value loaded by:	UVLO	UVLO	UVLO	UVLO	UVLO	UVLO	UVLO	UVLO
Read/write	R/W	R/W	R/W	R/W	R/W	R/W	R/W	R/W

LEGEND: R/W = Read/Write; R = Read only; -n = value after reset

**Table 15. PWM\_DUTY\_L Register Field Descriptions**

Bit	Field	Type	Reset	Description
Bit 7:0	PWM_DC[7:0]	R/W	00000000	Lower 8 bits for duty cycle of internally generated PWM on ISINK <sup>(1)(2)(3)</sup>

- (1) The default value in the register is 0x00. Any value written to the PWM\_DUTY\_1 and PWM\_DUTY\_2 registers is internally compared to PWM\_DUTY\_THR\_L and PWM\_DUTY\_THR\_H. A value below <PWM\_DUTY\_THR\_H><PWM\_DUTY\_THR\_L> is latched to the register but is internally ignored for setting the duty cycle and will result in a PWM signal with the minimum duty cycle defined by <PWM\_DUTY\_THR\_H><PWM\_DUTY\_THR\_L>
- (2) A new value in PWM\_DUTY\_L and PWM\_DUTY\_H is internally valid after writing to PWM\_DUTY\_H AND the dithering cycle is completed, therefore PWM\_DUTY\_L should be written to first.
- (3) A Duty Cycle of 1% or less may not be visible when the PWM frequency is 3KHz. At 24KHz, a Duty Cycle of 8% or less may not be visible.

**7.6.13 PWM\_DUTY\_H Register Address: 0Ch**
**Figure 29. PWM\_DUTY\_H Register**

PWM_DUTY_H	B7	B6	B5	B4	B3	B2	B1	B0
Bit name and function							PWM_DC[9]; MSB	PWM_DC[8]
Default	0	0	0	0	0	0	see Note1	see Note1
Default value loaded by:	UVLO	UVLO	UVLO	UVLO	UVLO	UVLO	UVLO	UVLO
Read/write	R	R	R	R	R	R	R/W	R/W

LEGEND: R/W = Read/Write; R = Read only; -n = value after reset

**Table 16. PWM\_DUTY\_H Register Field Descriptions**

Bit	Field	Type	Reset	Description
Bit 7:2		R	000000	
Bit 1:0	PWM_DC[9:8]	R/W	00	Higher 2 Bits for duty cycle of internally generated PWM on ISINK <sup>(1)(2)(3)</sup>
	PWM_DC[9:0]			00h = 0% duty cycle 3FFh = 99.9% duty cycle

- (1) The default value in the register is 0x00. Any value written to the PWM\_DUTY\_L and PWM\_DUTY\_H registers is internally compared to PWM\_DUTY\_THR\_L and PWM\_DUTY\_THR\_H. A value below <PWM\_DUTY\_THR\_H><PWM\_DUTY\_THR\_L> is latched to the register but is internally ignored for setting the duty cycle and will result in a PWM signal with the minimum duty cycle defined by <PWM\_DUTY\_THR\_H><PWM\_DUTY\_THR\_L>
- (2) A new value in PWM\_DUTY\_L and PWM\_DUTY\_H is internally valid after writing to PWM\_DUTY\_H AND the dithering cycle is completed, therefore PWM\_DUTY\_L should be written to first.
- (3) A Duty Cycle of 1% or less may not be visible when the PWM frequency is 3KHz. At 24KHz, a Duty Cycle of 8% or less may not be visible.

**7.6.14 MIN\_ON\_TIME Register Address: 0Dh**
**Figure 30. MIN\_ON\_TIME Register**

MIN_ON_TIME	B7	B6	B5	B4	B3	B2	B1	B0
Bit name and function	TIME[7]	TIME[6]	TIME[5]	TIME[4]	TIME[3]	TIME[2]	TIME[1]	TIME[0]
Default	0	0	0	0	0	0	0	0
Default value loaded by:	UVLO	UVLO	UVLO	UVLO	UVLO	UVLO	UVLO	UVLO
Read/write	R/W	R/W	R/W	R/W	R/W	R/W	R/W	R/W

LEGEND: R/W = Read/Write; R = Read only; -n = value after reset

**Table 17. MIN\_ON\_TIME Register Field Descriptions**

Bit	Field	Type	Reset	Description
Bit 7:0	TIME[7:0]	R/W	00000000	User register for setting the minimum-on-time for the LED. The LED will remain on for the time specified in the MIN_ON_TIME Register or the MIN_ON_TIME_THR Register whichever is greater provided the time is less than the duration of time for which the LED_EN pin remains asserted.

**7.6.15 SPARE Register Address: 0Eh**
**Figure 31. SPARE Register**

SPARE	B7	B6	B5	B4	B3	B2	B1	BO
Bit name and function	SPARE[7]	SPARE[6]	SPARE[5]	SPARE[4]	SPARE[3]	SPARE[2]	SPARE[1]	SPARE[0]
Default	0	0	0	0	0	0	0	0
Default value loaded by:	UVLO	UVLO	UVLO	UVLO	UVLO	UVLO	UVLO	UVLO
Read/write	R/W	R/W	R/W	R/W	R/W	R/W	R/W	R/W

LEGEND: R/W = Read/Write; R = Read only; -n = value after reset

**Table 18. SPARE Register Field Descriptions**

Bit	Field	Type	Reset	Description
Bit 7:0	SPARE[7:0]	R/W	00000000	Spare Register Bits

**7.6.16 4K\_OTP\_PASSWORD Register Address: 0Fh**
**Figure 32. 4K\_OTP\_PASSWORD Register**

4K_OTP_PASSWORD	B7	B6	B5	B4	B3	B2	B1	BO
Bit name and function	PW[7]	PW[6]	PW[5]	PW[4]	PW[3]	PW[2]	PW[1]	PW[0]
Default	0	0	0	0	0	0	0	0
Default value loaded by:	UVLO	UVLO	UVLO	UVLO	UVLO	UVLO	UVLO	UVLO
Read/write	W	W	W	W	W	W	W	W

LEGEND: R/W = Read/Write; R = Read only; -n = value after reset

**Table 19. 4K\_OTP\_PASSWORD Register Field Descriptions**

Bit	Field	Type	Reset	Description
Bit 7:0	PW[7:0]	W	00000000	User 4K OTP Password Register: The correct password enables the qualifier for writing to the User 4K OTP. The password is Implemented as a 2 Byte sequential write which must be performed back to back with no restriction on the delay between the writes. If the correct password is not set, writing to the User 4K OTP memory is disabled.

## 8 Application and Implementation

### NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

### 8.1 Application Information

The target application for the TPS657095 device is powering an embedded camera module.

### 8.2 Typical Application

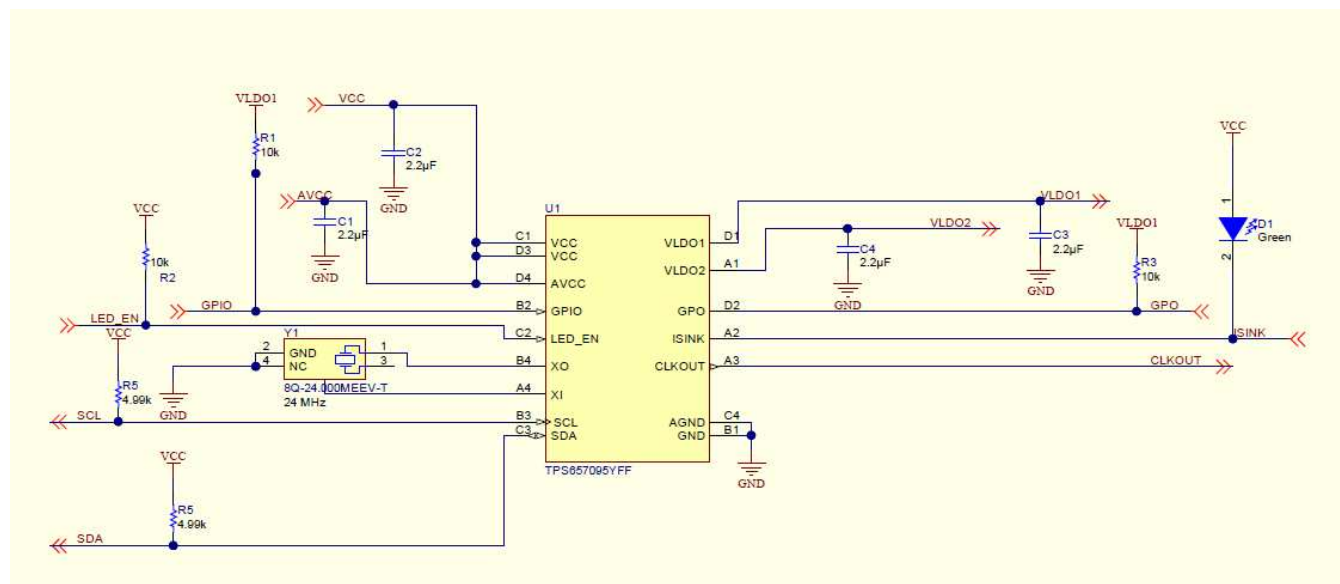


Figure 33. Application Schematic

#### 8.2.1 Design Requirements

Table 20. Design Parameters

DESIGN PARAMETER	VALUE
Typical Input Voltage	5.0V
LDO1 Output Voltage	1.8V (off by default)
LDO2 Output Voltage	1.2V (off by default)

#### 8.2.2 Detailed Design Procedure

##### 8.2.2.1 Output Capacitor Selection

The control loop of the LDOs is internally compensated such that they operate with small ceramic output capacitors of 2.2µF.

##### 8.2.2.2 Input Capacitor Selection

A low ESR input capacitor is required for best input voltage filtering and minimizing the interference with other circuits. The LDOs need a ceramic input capacitor with a minimum capacitance of 1.0µF. The input capacitor can be increased without any limit for better input voltage filtering.



**Table 21. Tested Capacitors**

TYPE	VALUE	VOLTAGE RATING	SIZE	SUPPLIER	MATERIAL
GRM155R60J225ME15D	2.2 $\mu$ F	6.3 V	0402	Murata	Ceramic X5R
GRM185R60J225	2.2 $\mu$ F	6.3 V	0603	Murata	Ceramic X5R
GRM185R60J105K	1 $\mu$ F	6.3 V	0603	Murata	Ceramic X5R

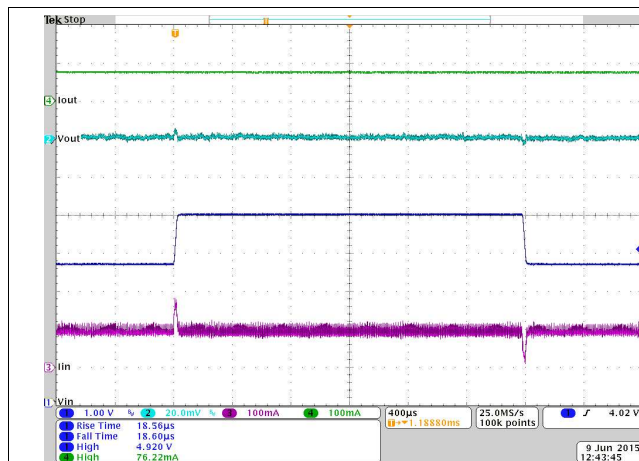
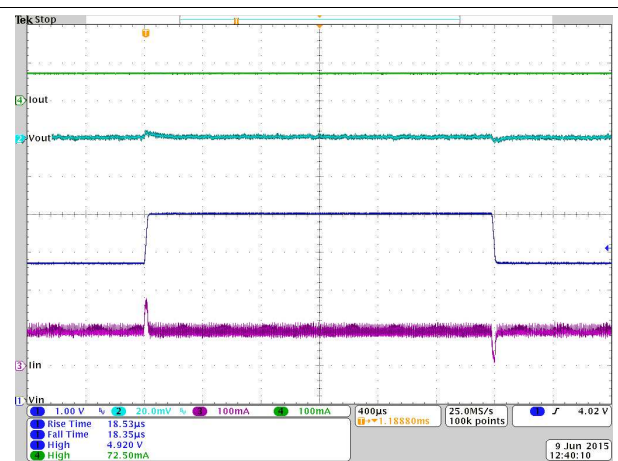
### 8.2.3 Application Curves

The graphs below were taken using the TPS657095EVM with the passive components as listed below:

- $C_{IN}(VCC) = GRM185R60J105K$  (1  $\mu$ F / 6.3V)
- $C_{OUT}(LDO1) = C_{OUT}(LDO2) = GRM185R60J225$  (2.2  $\mu$ F / 6.3 V)
- $V_{CC} = 5$  V unless otherwise noted

**Table 22. Table of Graphs**

DESCRIPTION		FIGURE
Line Transient Response LDO1	$V_{CC} = 3.6V$ to $5V$ to $3.6V$ ; $I_{OUT} = 75mA$ ; $V_{OUT} = 1.8V$	<a href="#">Figure 34</a>
Line Transient Response LDO2	$V_{CC} = 3.6V$ to $5V$ to $3.6V$ ; $I_{OUT} = 75mA$ ; $V_{OUT} = 2.8V$	<a href="#">Figure 35</a>
Load Transient Response LDO1	$V_{CC} = 5V$ ; $I_{OUT} = 7.5mA$ to $68mA$ to $7.5mA$ ; $V_{OUT} = 1.8V$	<a href="#">Figure 36</a>
Load Transient Response LDO2	$V_{CC} = 5V$ ; $I_{OUT} = 7.5mA$ to $68mA$ to $7.5mA$ ; $V_{OUT} = 2.8V$	<a href="#">Figure 37</a>
LDO1 and LDO2 Start-up Timing	$V_{CC} = 5V$ ; $I_{OUT} = 0mA$	<a href="#">Figure 38</a>
LDO1 and LDO2 Start-up Timing	$V_{CC} = 5V$ ; $I_{OUT} = 75mA$	<a href="#">Figure 39</a>
Duty Cycle on CLKout vs Programmed Frequency	$V_{CC} = 5V$ ; $f_{(crystal)} = 24MHz$ ; $V_{LDO1} = 1.8V$	<a href="#">Figure 40</a>
Period Jitter on CLKout vs Temperature and Output Frequency	$V_{CC} = 5V$ ; $f_{(crystal)} = 24MHz$ ; $V_{LDO1} = 1.8V$	<a href="#">Figure 41</a>


**Figure 34. Line Transient Response LDO1**

**Figure 35. Line Transient Response LDO2**

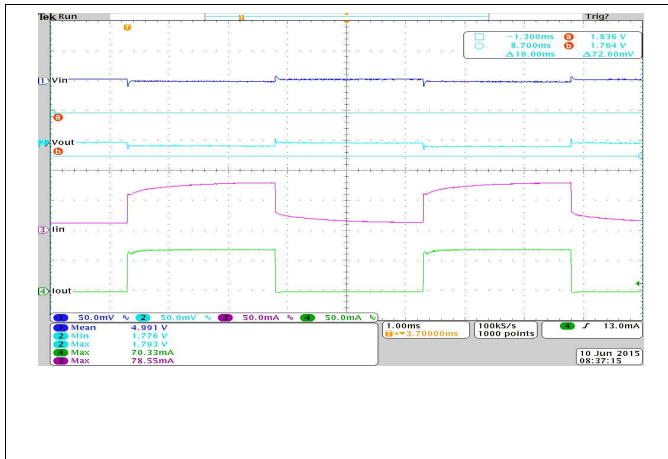


Figure 36. Load Transient Response LDO1

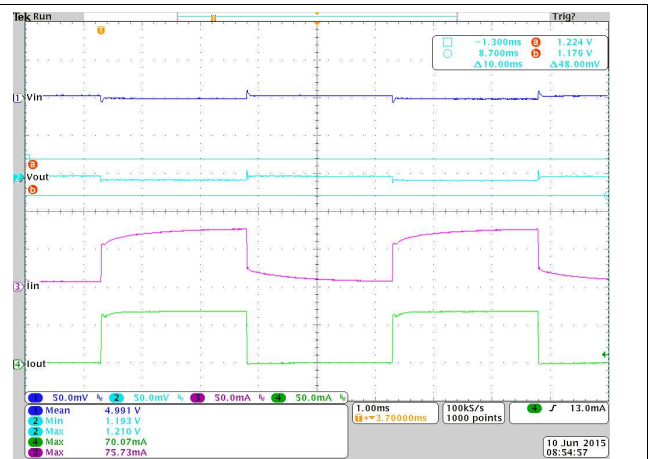


Figure 37. Load Transient Response LDO2

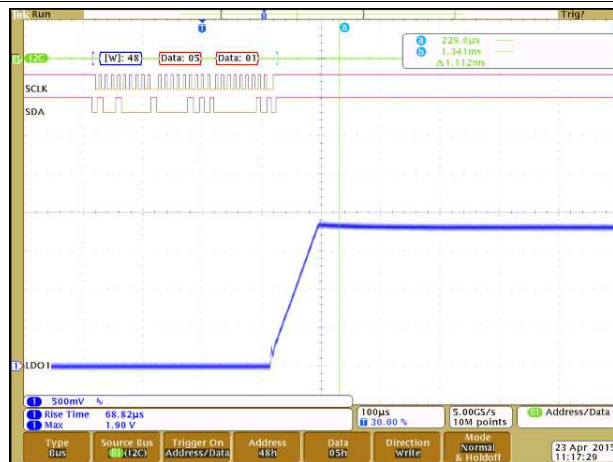


Figure 38. LDO1 Start-up Timing

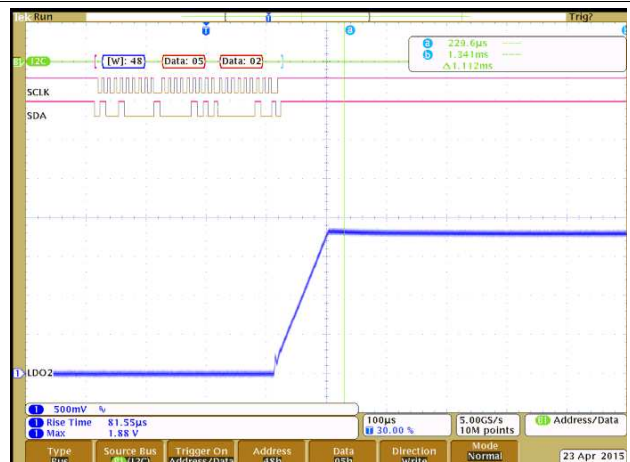


Figure 39. LDO2 Start-up Timing

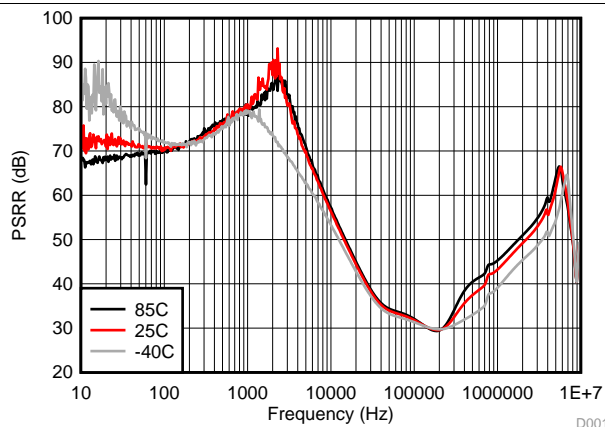


Figure 40. Duty Cycle

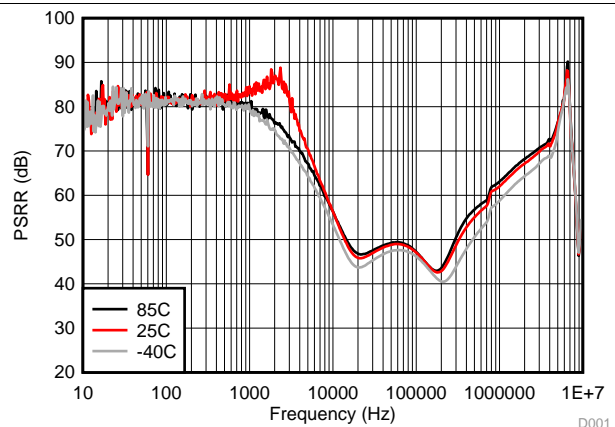


Figure 41. Period Jitter

## 9 Power Supply Recommendations

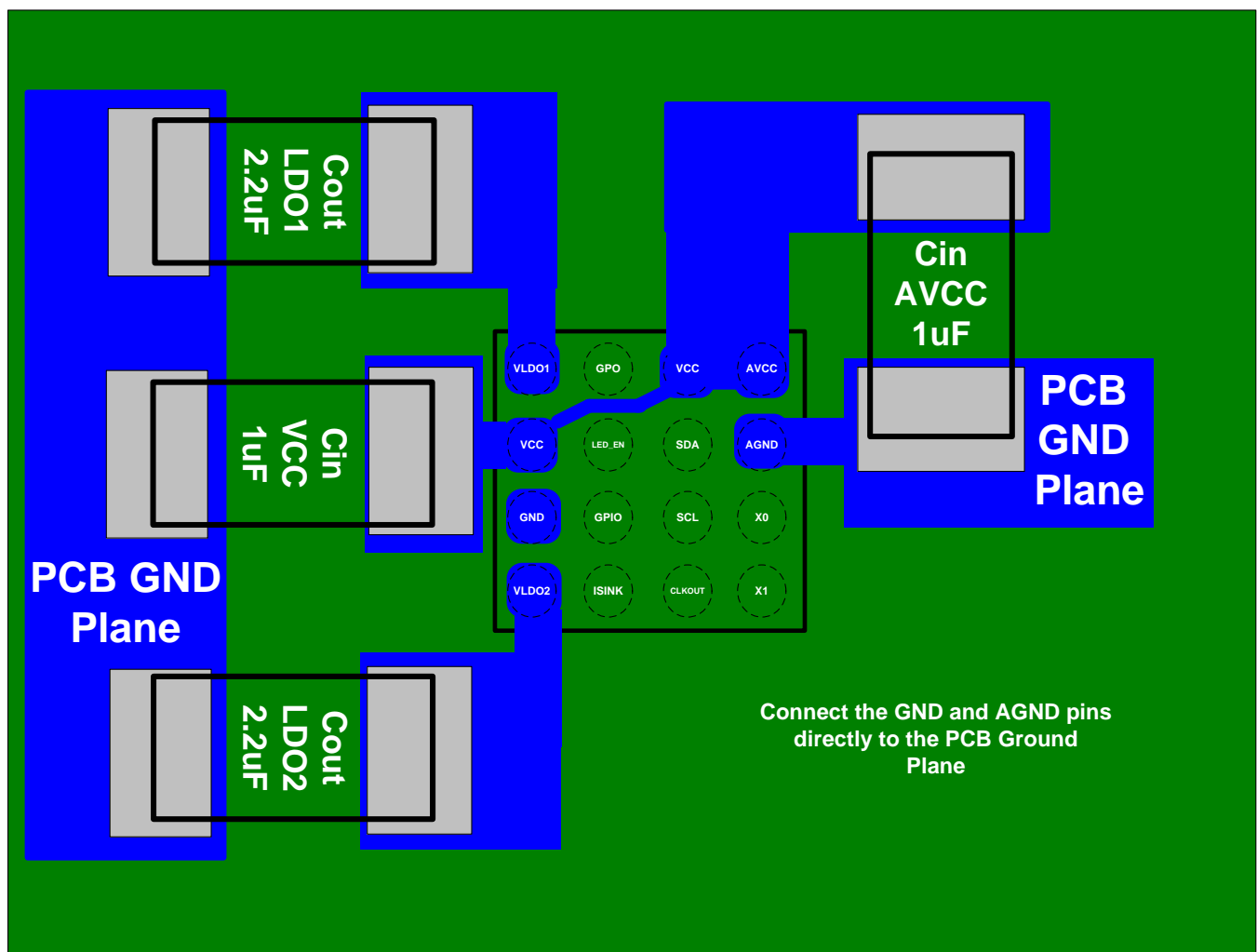
The TPS657095 devices are designed to operate from an input voltage range of 3.7V to 6.0V. The input supply should be well regulated.

## 10 Layout

### 10.1 Layout Guidelines

- The VCC and AVCC terminals should be bypassed to ground with a low ESR ceramic bypass capacitor. The typical recommended bypass capacitance is 1uF with a X5R or X7R dielectric.
- The optimum placement is closest to the AVCC terminal and the AGND terminal.
- The AGND and GND terminals should be tied to the pcb ground plane at the terminal of the IC

### 10.2 Layout Example



## 11 器件和文档支持

### 11.1 器件支持

#### 11.1.1 Third-Party Products Disclaimer

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### 11.5 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

## 12 机械、封装和可订购信息

以下页中包括机械、封装和可订购信息。 这些信息是针对指定器件可提供的最新数据。 这些数据会在无通知且不对本文档进行修订的情况下发生改变。 欲获得该数据表的浏览器版本，请查阅左侧的导航栏。

### 12.1 封装概要

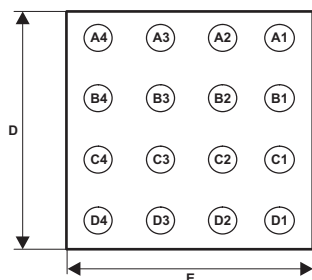


图 42. 芯片尺寸封装  
(底视图)

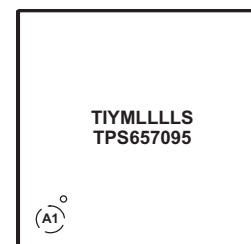


图 43. 芯片尺寸封装  
(顶视图)

代码:

- YM — 年月日代码

## 封装概要 (接下页)

- LLLL — 批次追踪代码
- S — 组装地点代码

## 12.2 芯片尺寸封装尺寸

TPS657095 器件采用 16 焊锡凸块芯片尺寸封装 (YFF, NanoFree™)。封装尺寸如下:

- D = ca.  $1700 \pm 25\mu\text{m}$
- E = 大约  $1700 \pm 25\mu\text{m}$

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	产品		应用
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数据转换器	<a href="http://www.ti.com.cn/dataconverters">www.ti.com.cn/dataconverters</a>	消费电子	<a href="http://www.ti.com.cn/consumer-apps">www.ti.com.cn/consumer-apps</a>
DLP® 产品	<a href="http://www.dlp.com">www.dlp.com</a>	能源	<a href="http://www.ti.com.cn/energy">www.ti.com.cn/energy</a>
DSP - 数字信号处理器	<a href="http://www.ti.com.cn/dsp">www.ti.com.cn/dsp</a>	工业应用	<a href="http://www.ti.com.cn/industrial">www.ti.com.cn/industrial</a>
时钟和计时器	<a href="http://www.ti.com.cn/clockandtimers">www.ti.com.cn/clockandtimers</a>	医疗电子	<a href="http://www.ti.com.cn/medical">www.ti.com.cn/medical</a>
接口	<a href="http://www.ti.com.cn/interface">www.ti.com.cn/interface</a>	安防应用	<a href="http://www.ti.com.cn/security">www.ti.com.cn/security</a>
逻辑	<a href="http://www.ti.com.cn/logic">www.ti.com.cn/logic</a>	汽车电子	<a href="http://www.ti.com.cn/automotive">www.ti.com.cn/automotive</a>
电源管理	<a href="http://www.ti.com.cn/power">www.ti.com.cn/power</a>	视频和影像	<a href="http://www.ti.com.cn/video">www.ti.com.cn/video</a>
微控制器 (MCU)	<a href="http://www.ti.com.cn/microcontrollers">www.ti.com.cn/microcontrollers</a>		
RFID 系统	<a href="http://www.ti.com.cn/rfidsys">www.ti.com.cn/rfidsys</a>		
OMAP应用处理器	<a href="http://www.ti.com/omap">www.ti.com/omap</a>		
无线连通性	<a href="http://www.ti.com.cn/wirelessconnectivity">www.ti.com.cn/wirelessconnectivity</a>	德州仪器在线技术支持社区	<a href="http://www.deyisupport.com">www.deyisupport.com</a>

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**PACKAGING INFORMATION**

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TPS657095YFFR	ACTIVE	DSBGA	YFF	16	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 85	TPS 657095	
TPS657095YFFT	ACTIVE	DSBGA	YFF	16	250	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 85	TPS 657095	

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

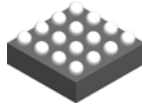
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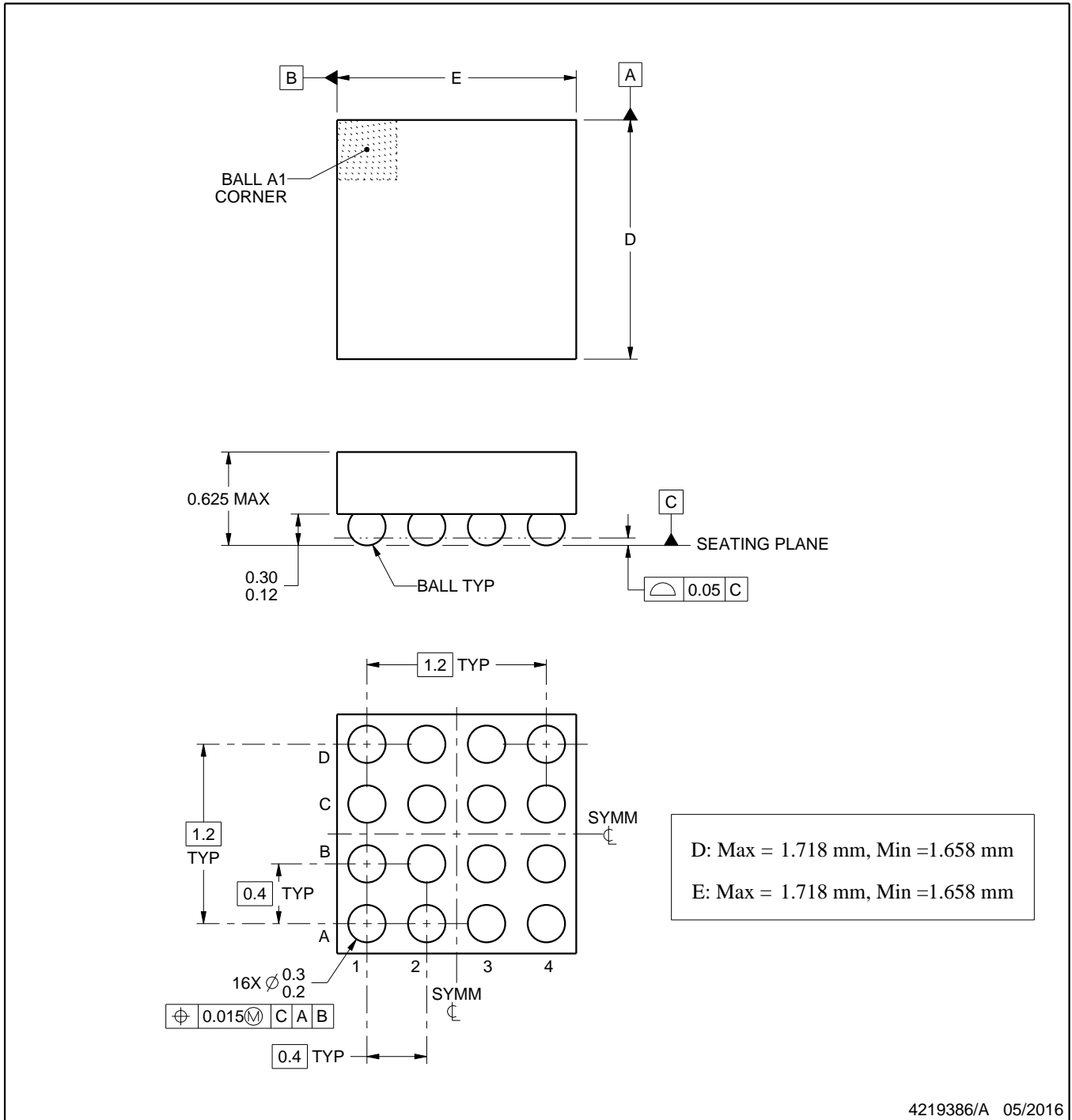
YFF0016



PACKAGE OUTLINE

DSBGA - 0.625 mm max height

DIE SIZE BALL GRID ARRAY



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NOTES:

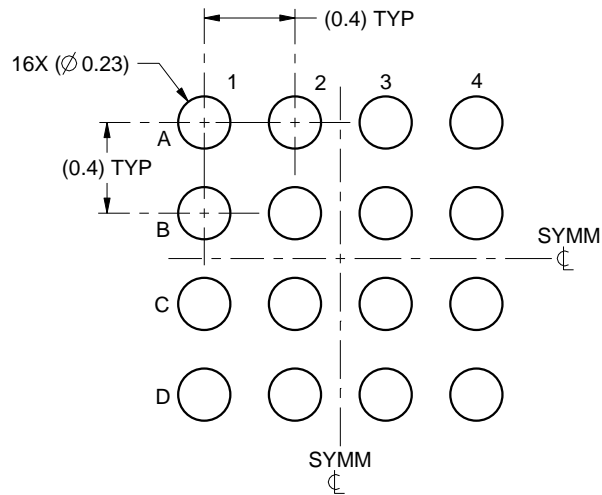
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.

# EXAMPLE BOARD LAYOUT

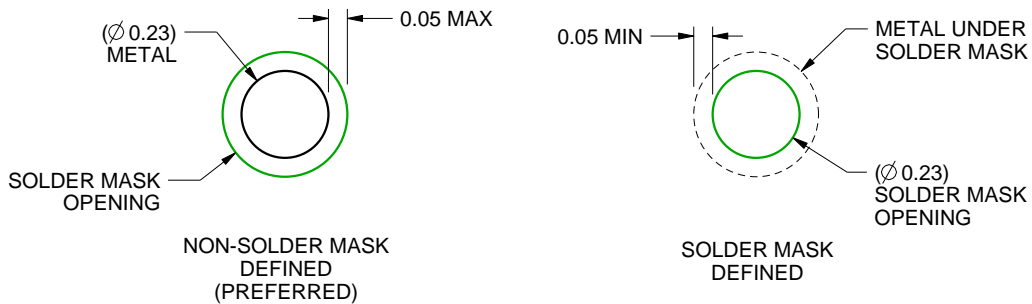
YFF0016

DSBGA - 0.625 mm max height

DIE SIZE BALL GRID ARRAY



LAND PATTERN EXAMPLE  
SCALE:30X



SOLDER MASK DETAILS  
NOT TO SCALE

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NOTES: (continued)

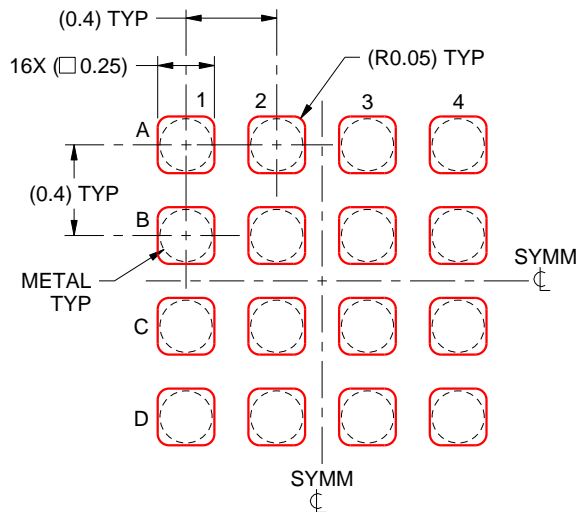
3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SNVA009 ([www.ti.com/lit/snva009](http://www.ti.com/lit/snva009)).

# EXAMPLE STENCIL DESIGN

YFF0016

DSBGA - 0.625 mm max height

DIE SIZE BALL GRID ARRAY



SOLDER PASTE EXAMPLE  
BASED ON 0.1 mm THICK STENCIL  
SCALE:30X

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NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.

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